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Furuya

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(54) **METHOD FOR PRODUCING OPTICAL ASSEMBLY AND OPTICAL ASSEMBLY**

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CPC **G02B 6/4231** (2013.01); **G02B 6/428**
(2013.01)

(58) **Field of Classification Search**
CPC **G02B 6/4231**; **G02B 6/428**
See application file for complete search history.

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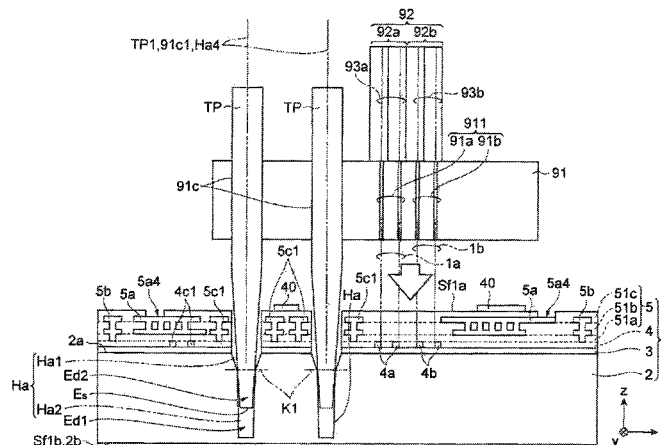
Primary Examiner — Peter Radkowski

(74) Attorney, Agent, or Firm — Smith, Gambrell & Russell, LLP.

(57) **ABSTRACT**

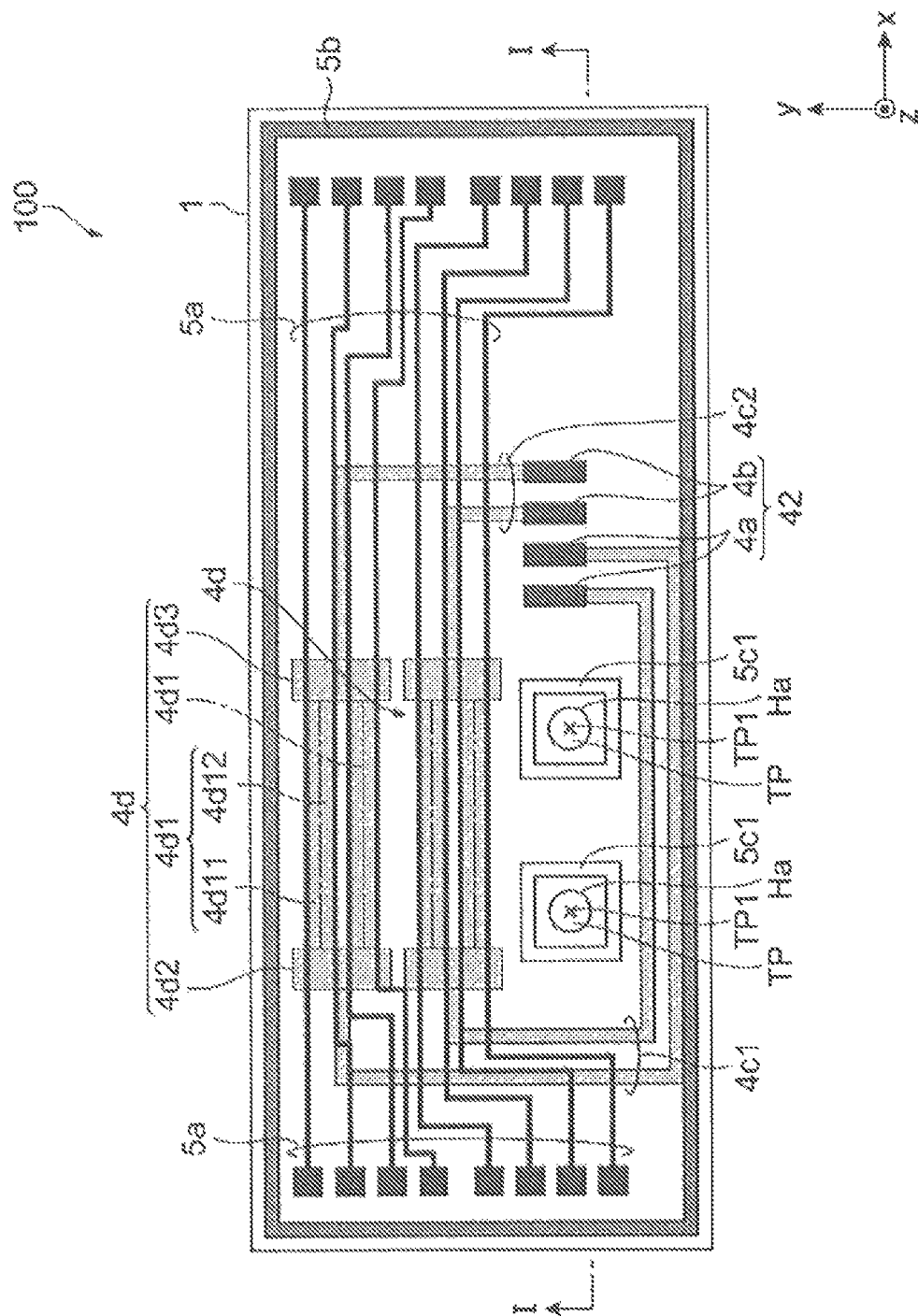
A method for producing an optical assembly includes the steps of forming an optical semiconductor device including a substrate, a recess and an first optical waveguide, the optical semiconductor device having a principal surface, the recess extending from the principal surface to a middle portion of the substrate; forming an optical waveguide device including a through-hole and a second optical waveguide; positioning the optical semiconductor device and the optical waveguide device so that the principal surface of the optical semiconductor device and a back surface of the optical waveguide device face each other; aligning the optical semiconductor device and the optical waveguide device by inserting a guide pin into the through-hole and the recess so that the first optical waveguide is optically coupled with the second optical waveguide; and joining the optical semiconductor device and the optical waveguide device to each other.

12 Claims, 12 Drawing Sheets



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FIG. 1



2GFI

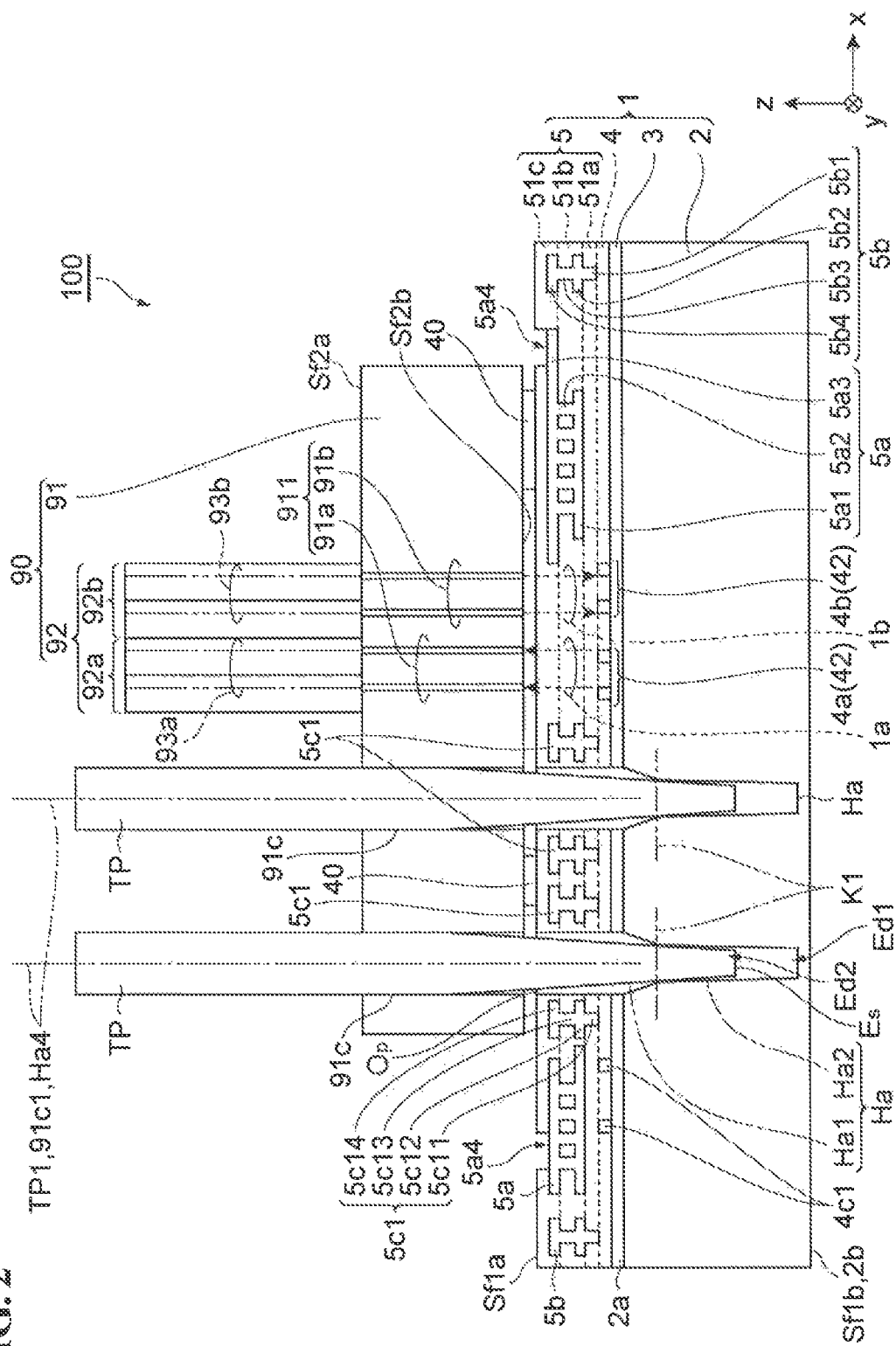


FIG. 3

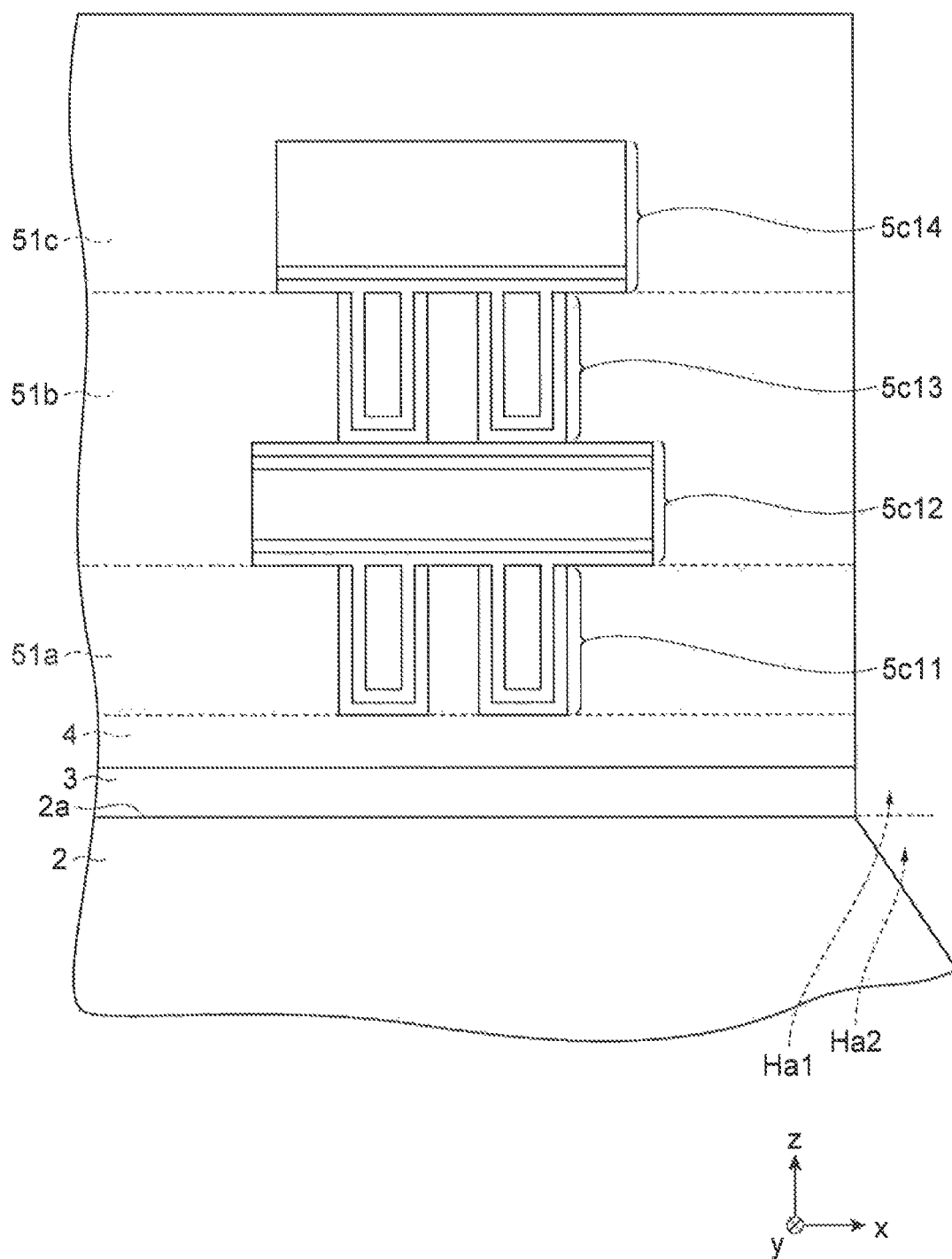


FIG. 4A

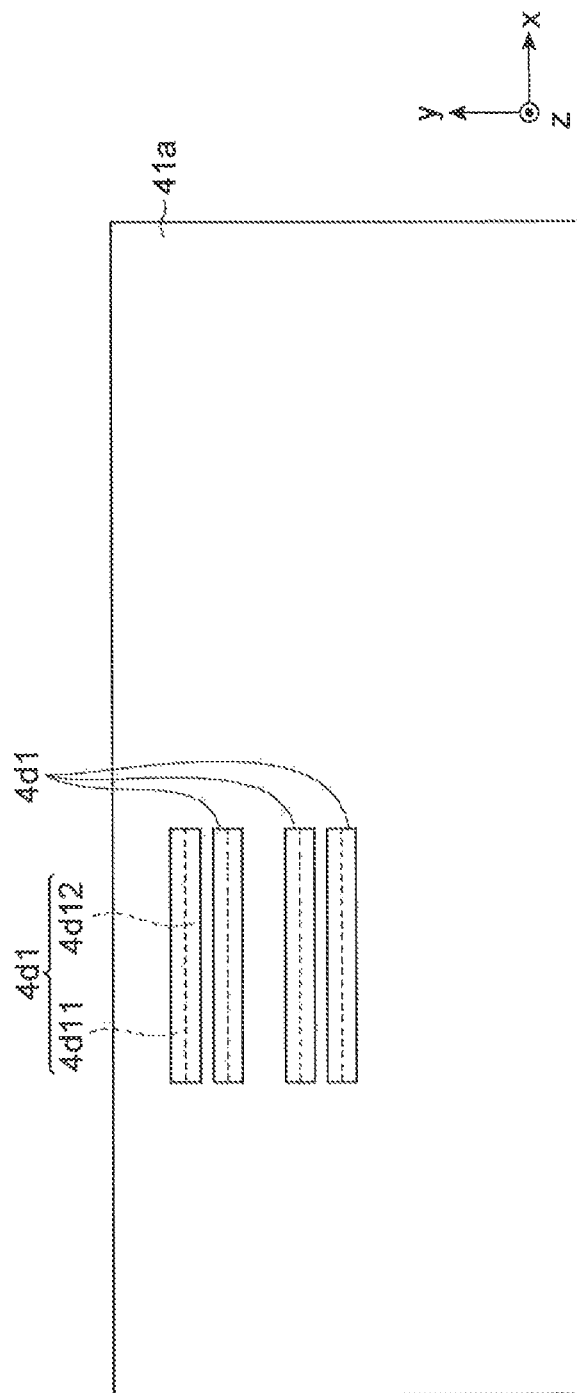


FIG. 4B

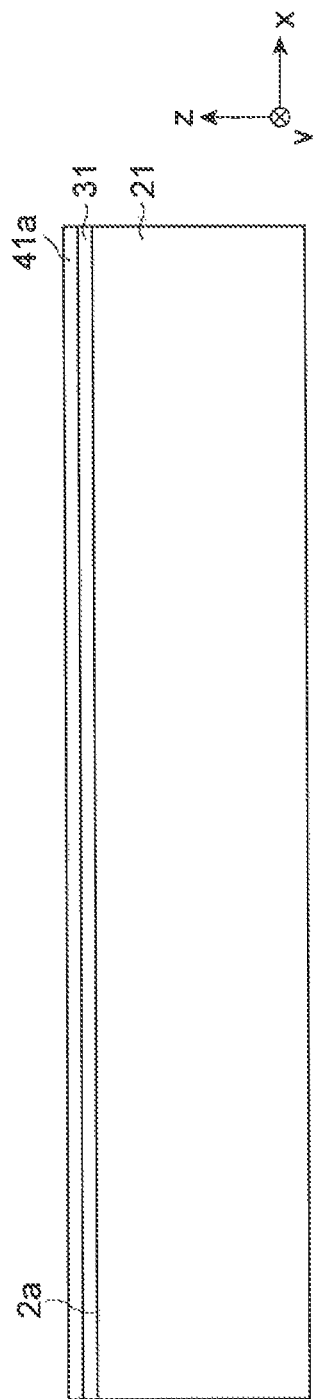


FIG. 5A

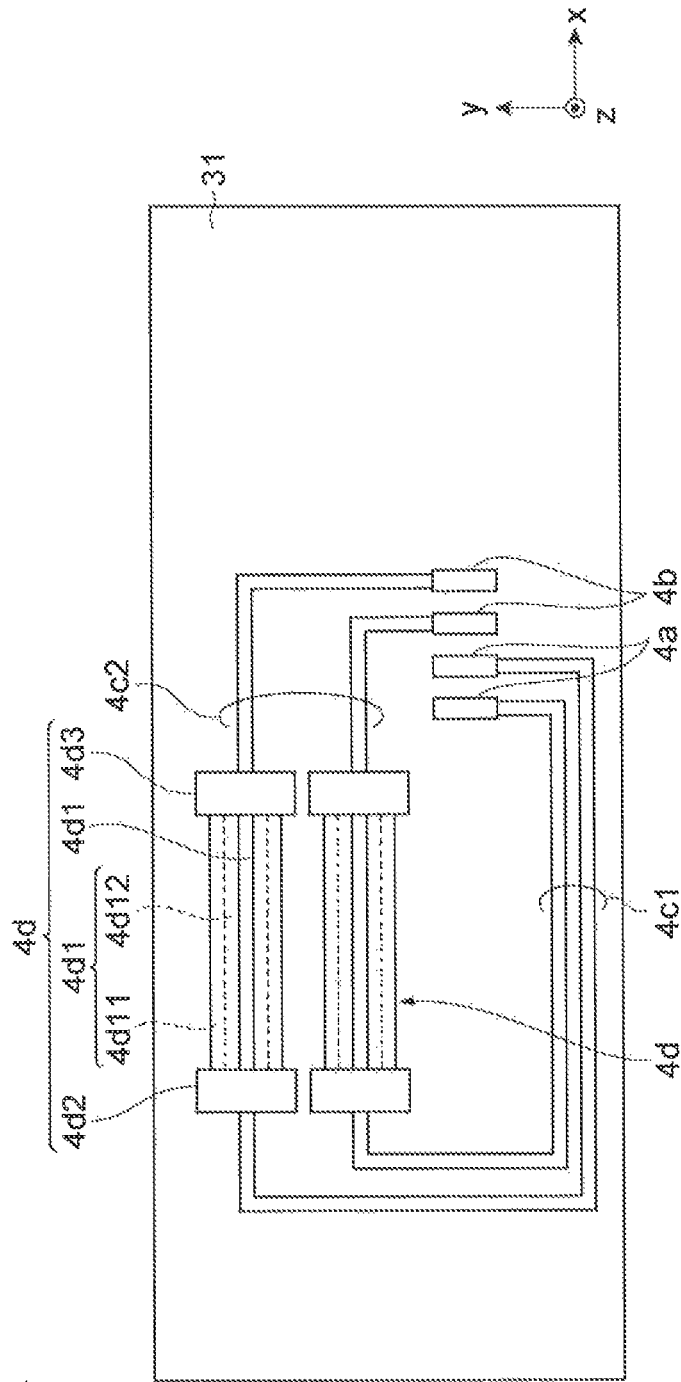


FIG. 5B

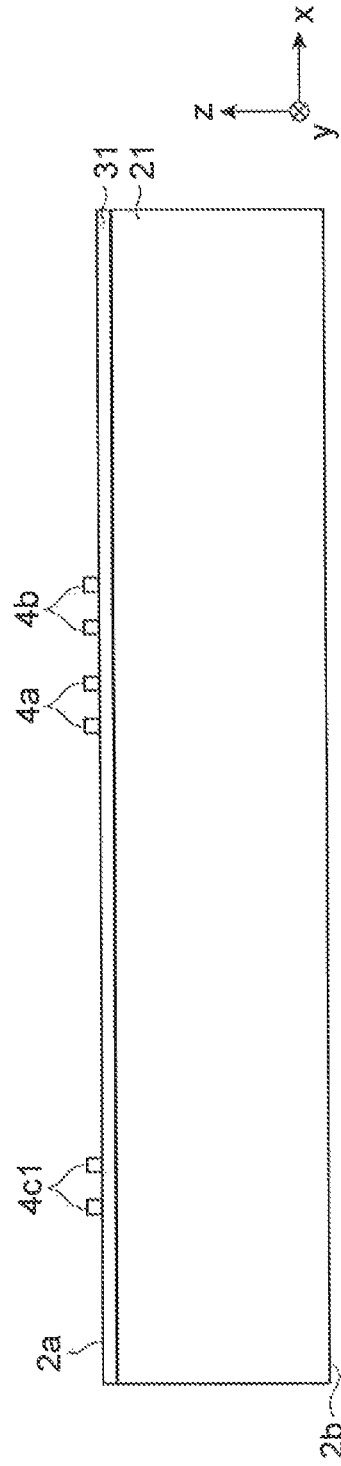


FIG. 6

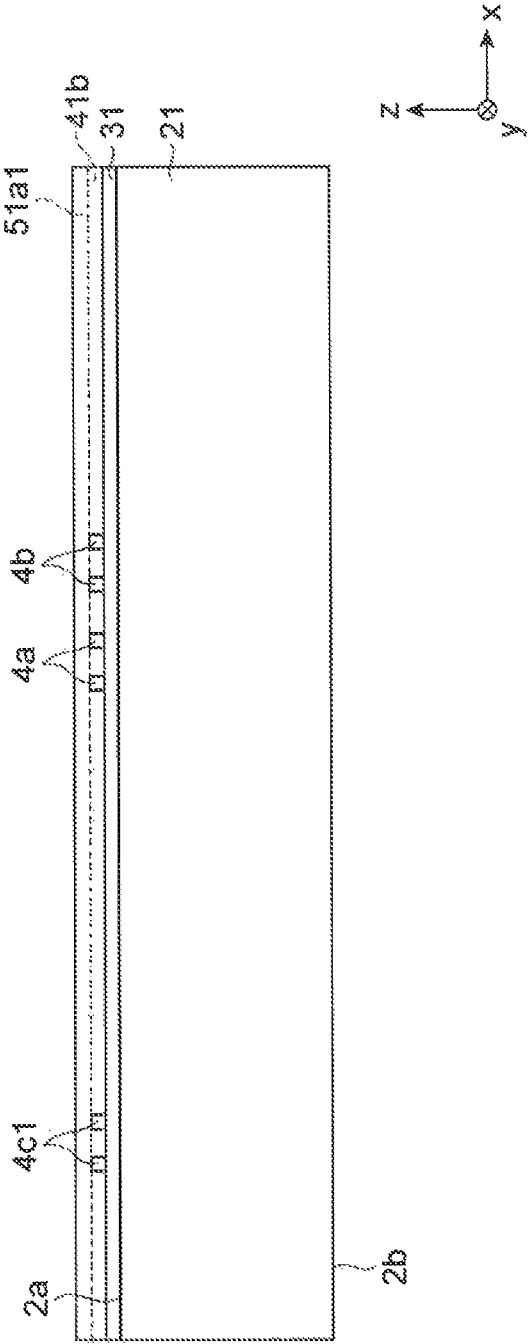


FIG. 7A

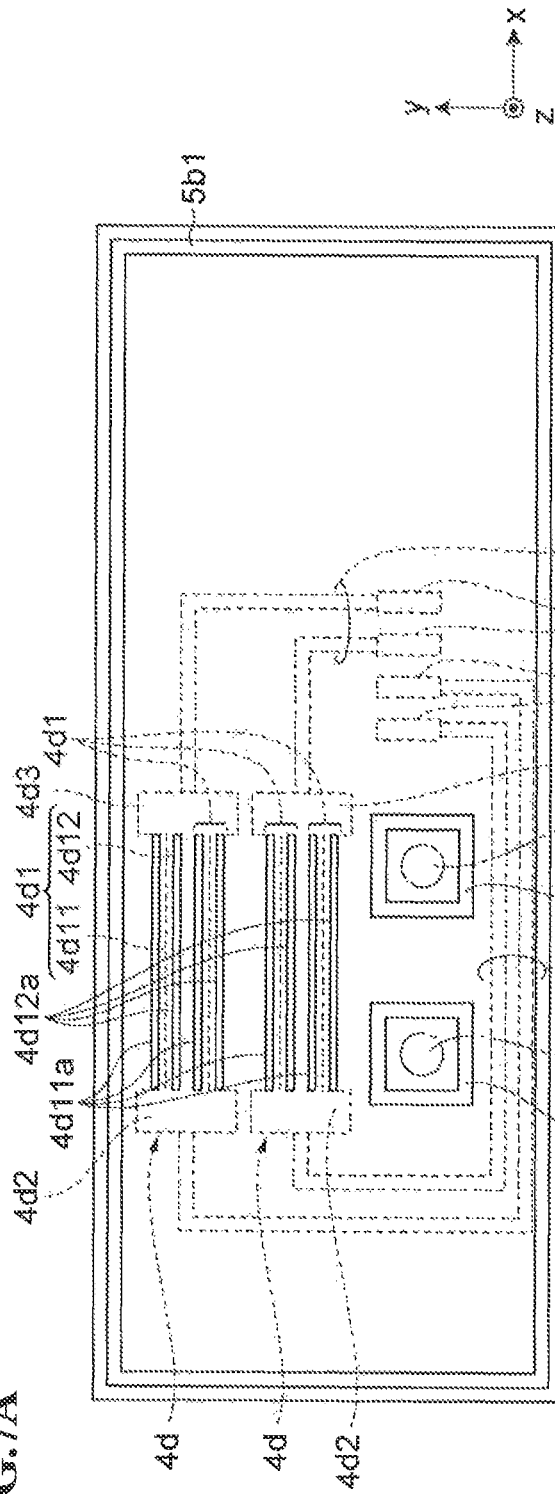


FIG. 7B

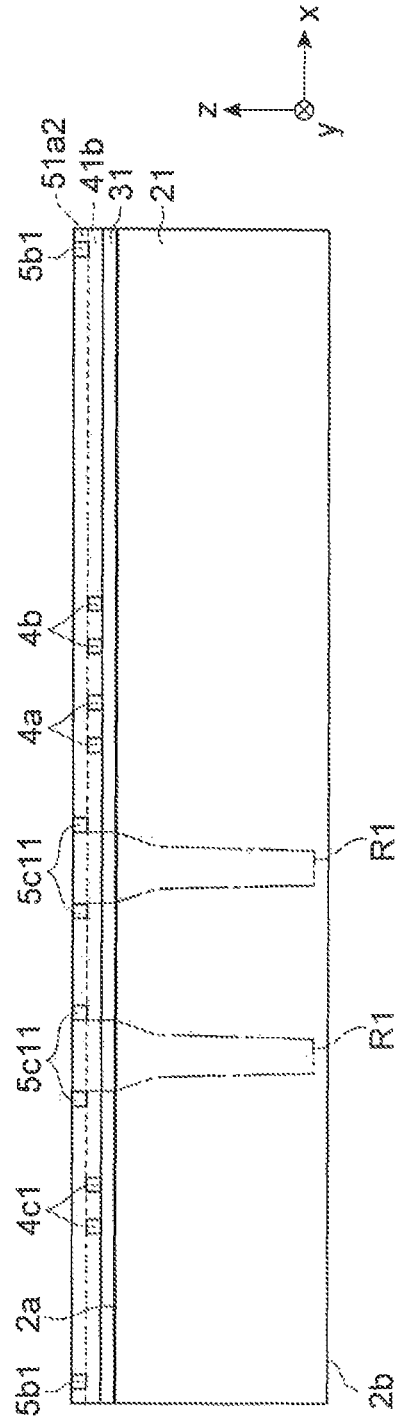


FIG. 8A

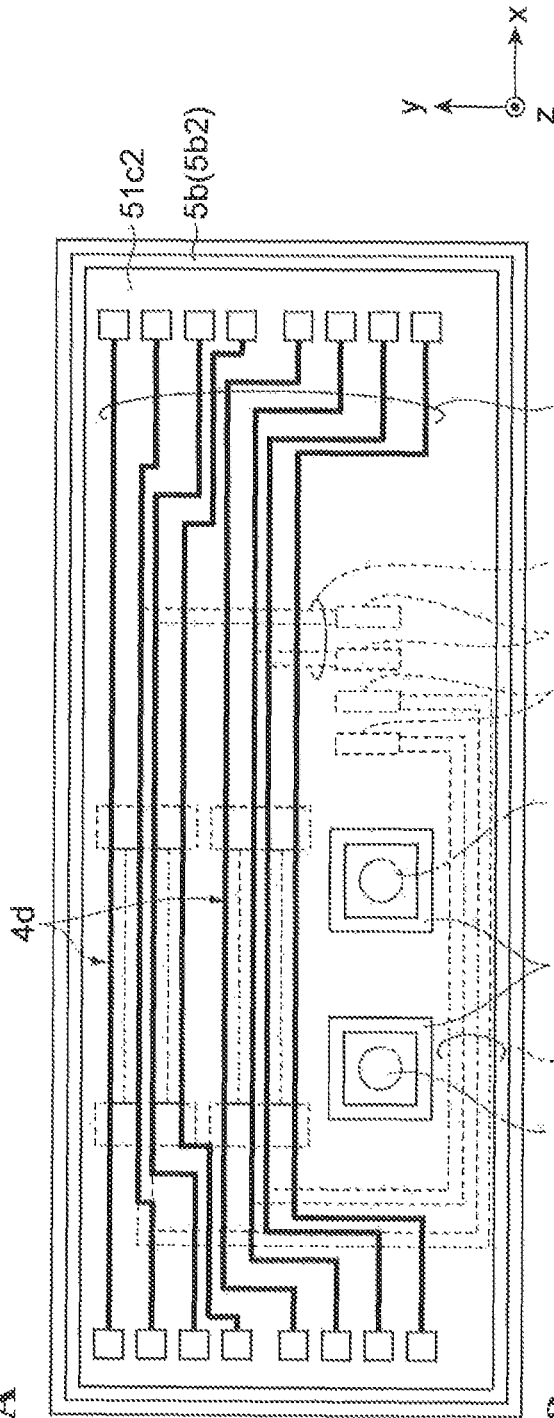


FIG. 8B

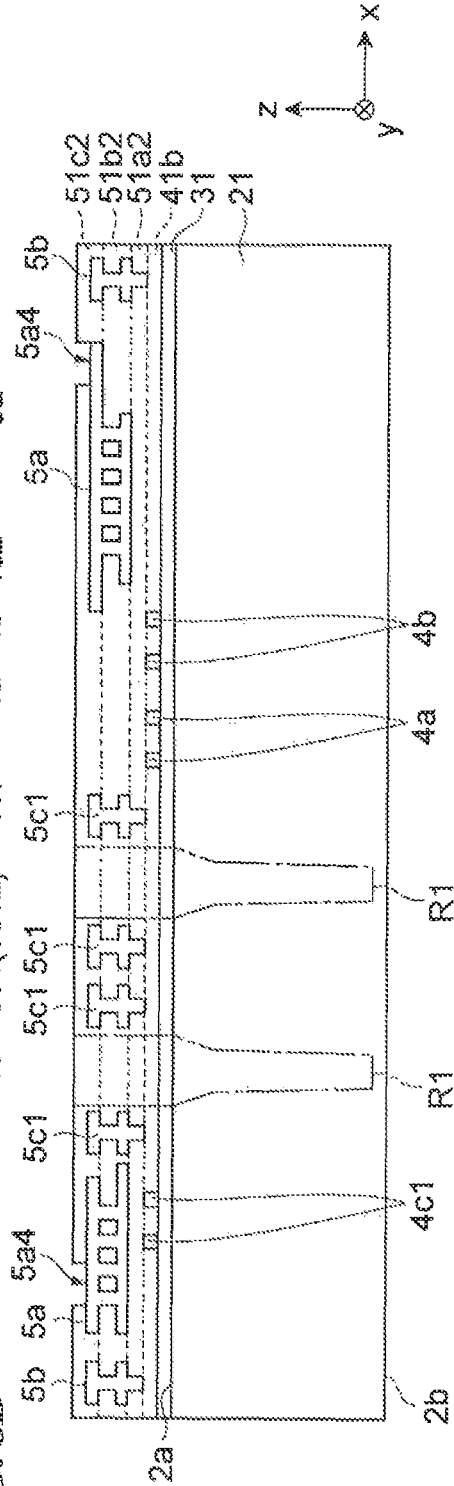


FIG. 9A

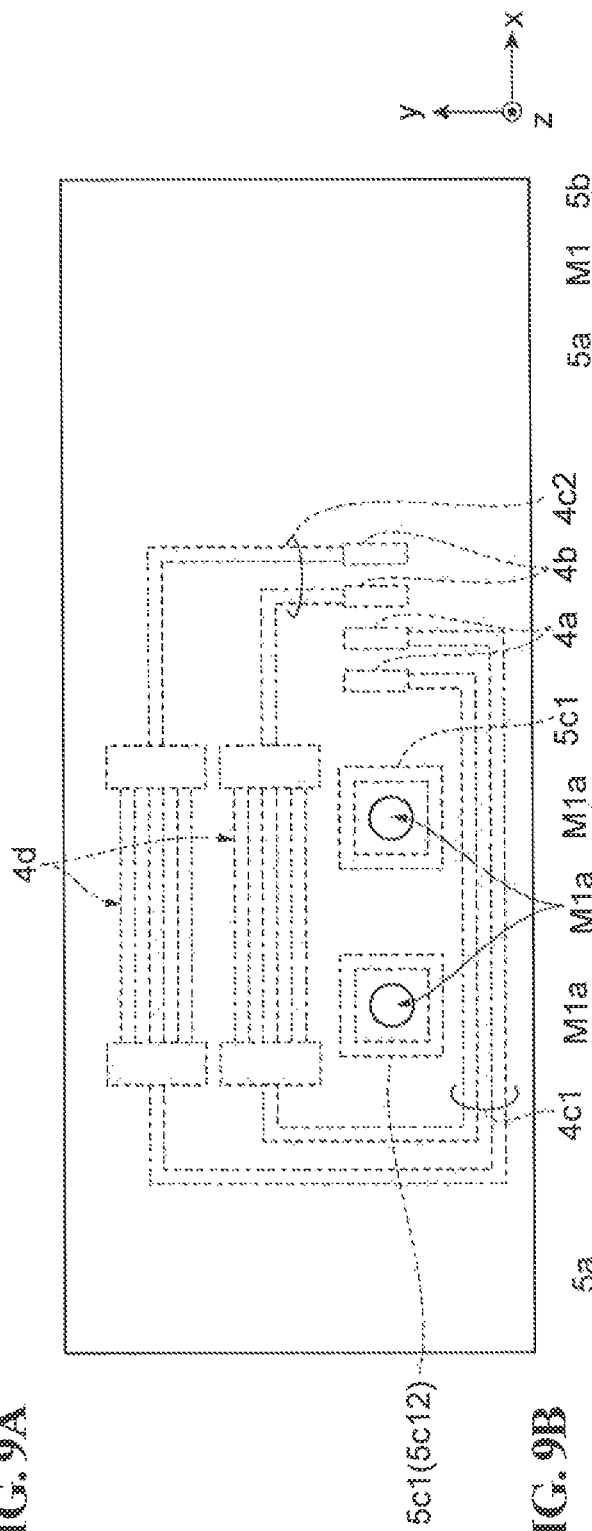


FIG. 9B

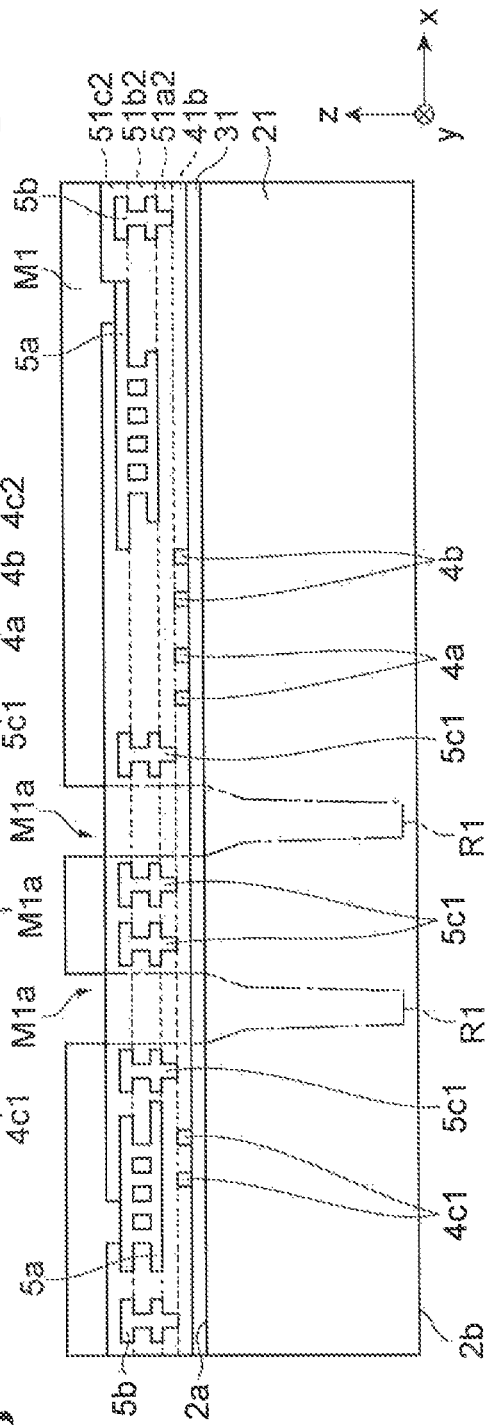


FIG. 10A

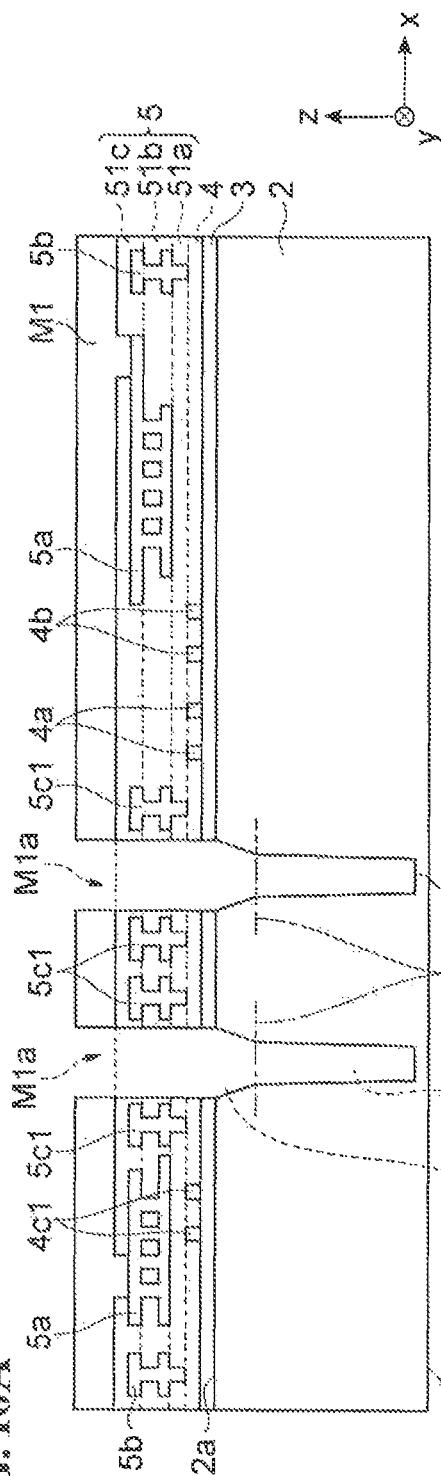


FIG. 10B

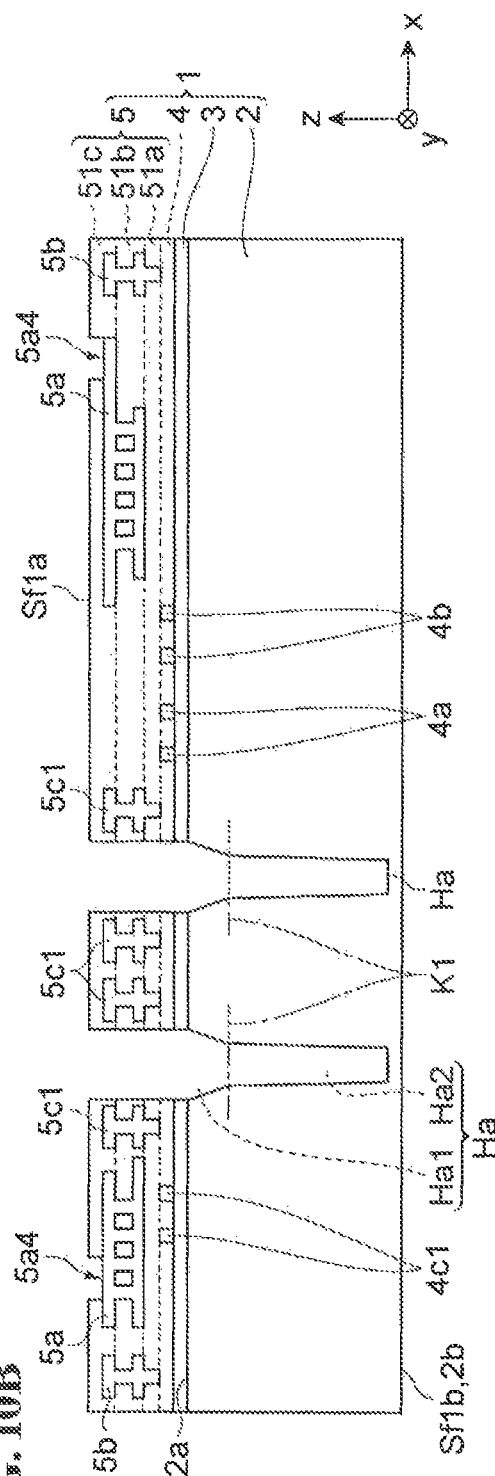


Fig. 1

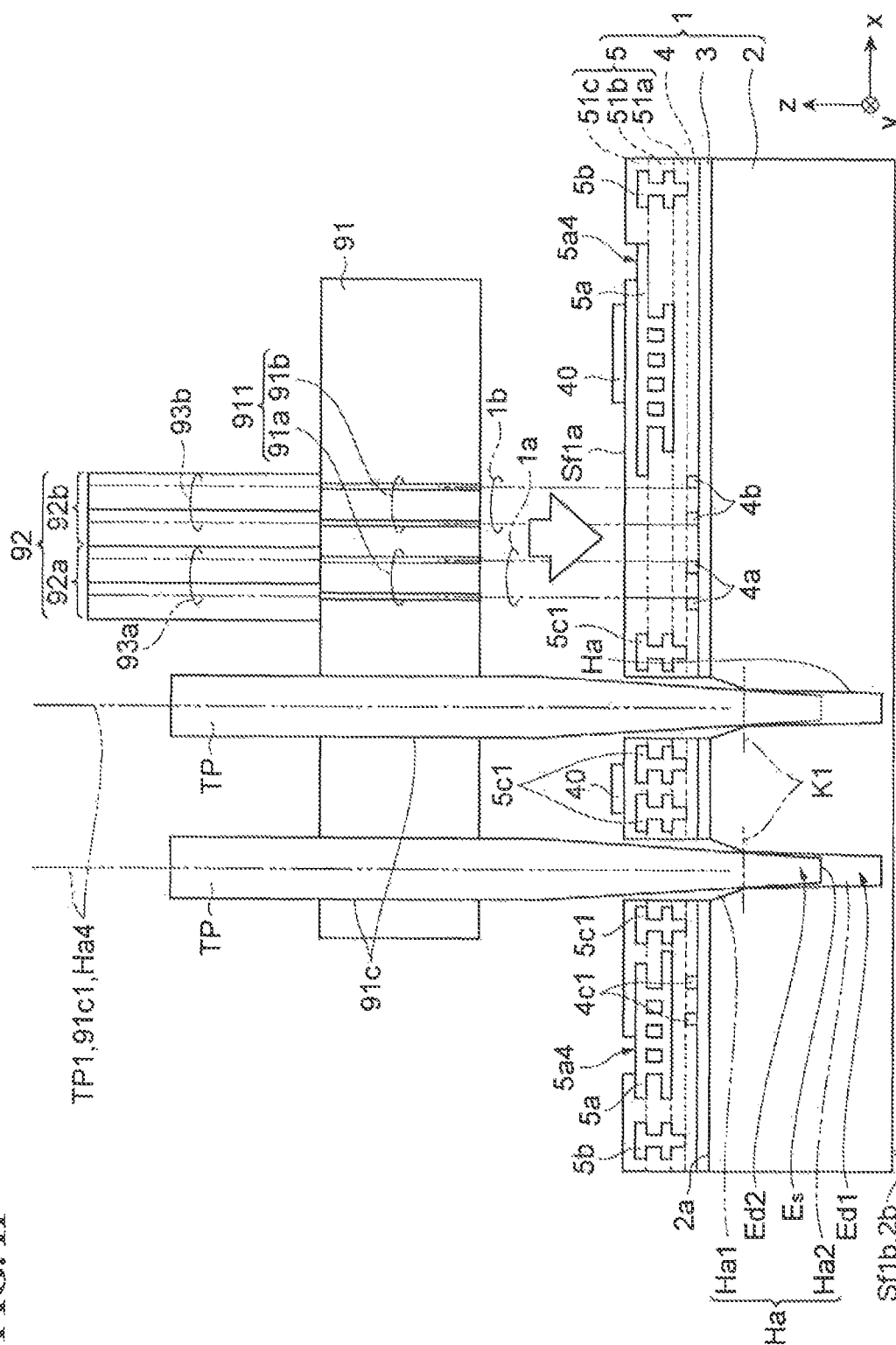
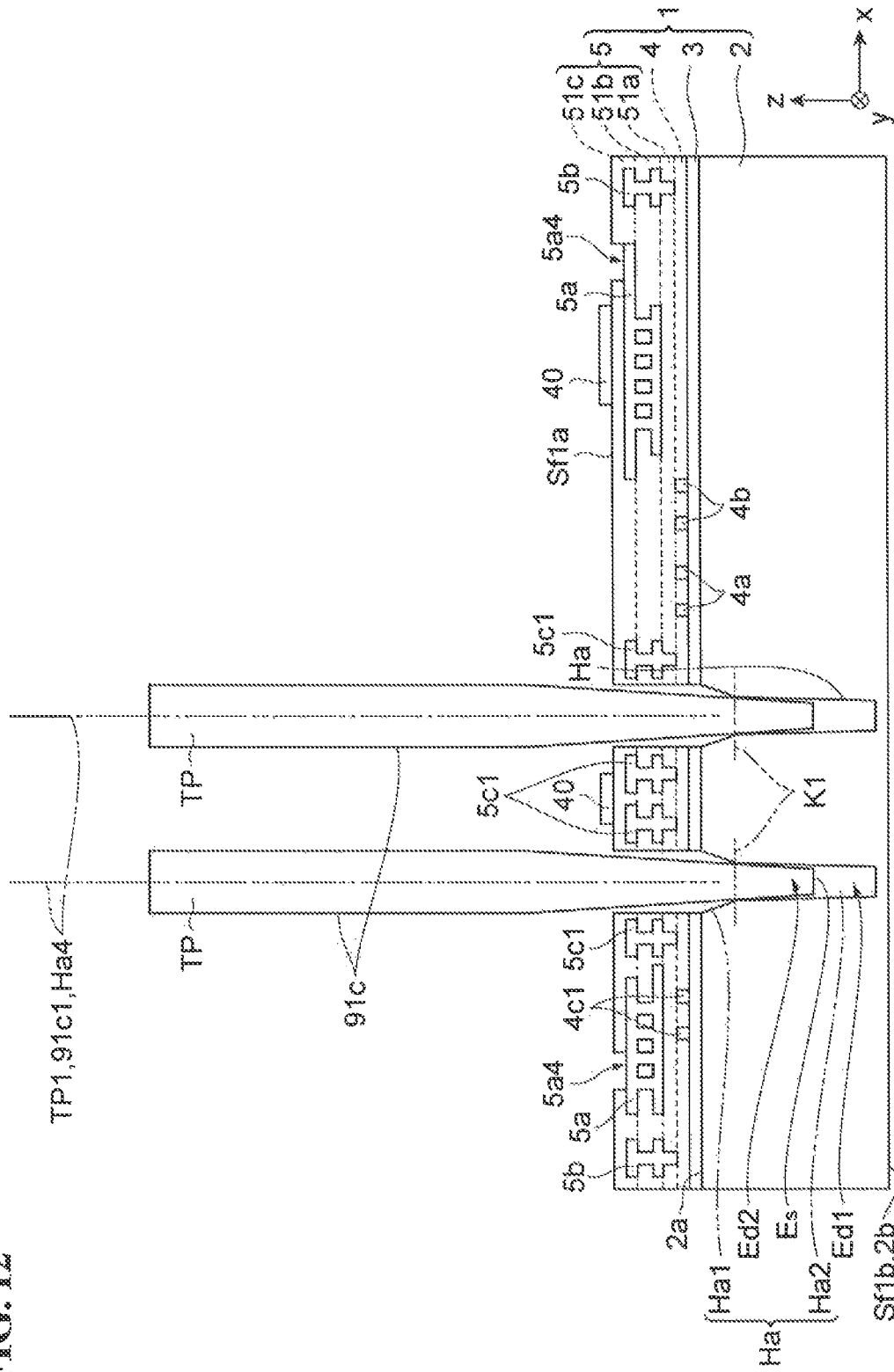


FIG. 12



METHOD FOR PRODUCING OPTICAL ASSEMBLY AND OPTICAL ASSEMBLY

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to a method for producing an optical assembly and the optical assembly.

2. Description of the Related Art

Japanese Unexamined Patent Application Publication No. 2012-256869 (Patent Literature 1) discloses a method for integrating various photonic devices on a silicon photonics platform. This method includes the steps of providing a planarized silicon-based photonic substrate including a silicon (Si) waveguide structure, depositing a dielectric layer (such as a silicon oxide (SiO₂) layer) on a top portion of the planarized silicon-based photonic substrate, selectively etching the dielectric layer, thereby exposing a portion of the silicon waveguide structure, using the silicon waveguide structure as a seed layer to selectively grow in the template a germanium (Ge) layer that extends above the dielectric layer, and planarizing the germanium layer to form a planarized germanium layer having a reduced thickness of 100 nm to 500 nm.

Japanese Unexamined Patent Application Publication No. 2012-133363 (Patent Literature 2) discloses an optical modulator and an optical transmitter including the optical modulator. The optical modulator includes a light input/output unit, an optical waveguide, and a phase shifter. The light input/output unit includes a vertical grating coupler or a slanted grating coupler. The light input/output unit receives an unmodulated input light signal, divides the input light signal into a first light signal and a second light signal, and transmits the first light signal and the second light signal to a first path and a second path of the optical waveguide, respectively. The phase shifter is positioned in at least one of the first path and the second path, modulates the phase of at least one of the first light signal that is transmitted through the first path and the second light signal that is transmitted through the second path using an electrical signal, and outputs the modulated light signal as a phase modulated signal.

SUMMARY OF THE INVENTION

In recent years, an optical waveguide and an optical waveguide device such as an optical modulator are produced by processing a silicon (Si) layer on a silicon-on-insulator (SOI) substrate using a silicon complementary metal-oxide semiconductor (Si-CMOS) integrated circuit (IC) micromachining technique. Further, an optical semiconductor integrated device in which the optical waveguide and the optical waveguide device are integrated is being commercialized. For example, by processing a silicon (Si) layer on an SOI substrate, an optical waveguide, a modulator, and a grating coupler are fabricated. Further, by forming a germanium (Ge) layer and a wiring structure on the optical waveguide, the modulator, and the grating coupler, a PIN light-receiving device is formed. An optical semiconductor device in which a plurality of PIN light-receiving devices are monolithically integrated and each of wirings is connected to one of the PIN light-receiving devices is fabricated by using a conventional method such as the Si-CMOS IC micromachining technique. Optical transmitters and optical receivers are also fabricated by using this method. In such a conventional optical semiconductor device, input and output of light are optically coupled to an external optical waveguide (such as an optical

fiber) at a surface of the optical semiconductor device through the grating coupler formed in the silicon (Si) layer. Therefore, the optical fiber is connected to the surface of the optical semiconductor device. It is important to produce the optical semiconductor device by applying an ordinary design rule/production process for fabricating the Si-CMOS IC so as to produce the optical semiconductor device at a low cost by using the Si-CMOS IC micromachining technique. Therefore, a device structure and a production process of the conventional optical semiconductor device become similar to those used for the CMOS IC.

In high-speed and long-distance optical transmission systems, a single-mode optical fiber is used as an optical waveguide in order to prevent deterioration of a transmission waveform caused by mode dispersion of an optical fiber. Usually, in the high-speed and long-distance optical transmission systems, near-infrared light having a wavelength of 1.3 μm to 1.6 μm is used because an optical fiber has a low optical loss in the wavelength band of 1.3 μm to 1.6 μm . In this case, the single-mode optical fiber using in the high-speed and long-distance transmission systems has a core whose diameter is about 8 μm . Therefore, in order to couple the conventional optical semiconductor device to the single-mode optical fiber with a high efficiency, a mode size of an incident light into the grating coupler or a mode size of an output light from the grating coupler is designed to be about 8 μm . In this case, the optical semiconductor device and the optical waveguide device such as a single-mode optical fiber are optically aligned with an exact precision on the order of less than or equal to ± 2 μm with respect to the position of an optimal point. Hitherto, the optical alignment between the optical semiconductor device and the optical waveguide device (single-mode optical fiber) is performed by what is called an active alignment method. That is, in the active alignment method, first, the position of the optical semiconductor device and the position of the optical waveguide device are adjusted with respect to each other while light is, actually, output to the optical semiconductor device from the optical waveguide device or to the optical waveguide device from the optical semiconductor device. Next, a point where optical coupling between the optical semiconductor device and the optical waveguide device becomes a maximum is determined while adjusting the position of the optical semiconductor device and the position of the optical waveguide device with respect to each other. By using resin, solder, or the like, the optical semiconductor device and the optical waveguide device are secured at the point where the optical coupling becomes a maximum. However, in the active alignment method, it takes effort and time to align the optical semiconductor device and the optical waveguide device with respect to each other.

A method for producing an optical assembly according to the present invention includes the steps of forming an optical semiconductor device having a first principal surface and a first back surface opposite to the first principal surface, the optical semiconductor device including a substrate, a recess formed on the first principal surface, and an first optical waveguide formed on the substrate, the recess having a first center axis substantially orthogonal to the first principal surface; forming an optical waveguide device having a second principal surface and a second back surface opposite to the second principal surface, the optical waveguide device including a through-hole having a second center axis substantially orthogonal to the second back surface, and a second optical waveguide, the through-hole penetrating through the second principal surface and the second back surface; positioning the optical semiconductor device and

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the optical waveguide device so that the first principal surface and the second back surface face each other; aligning the optical semiconductor device and the optical waveguide device by inserting a guide pin into the through-hole and the recess, the first center axis of the recess and the second center axis of the through-hole being aligned with each other; and joining the optical semiconductor device and the optical waveguide device to each other. The recess is extended from the first principal surface to a middle portion of the substrate. In addition, in the step of aligning the optical semiconductor device and the optical waveguide device, the first optical waveguide of the optical semiconductor device is optically coupled with the second optical waveguide of the optical waveguide device.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 shows a main internal structure of an optical semiconductor device according to an embodiment as seen from an x-y plane.

FIG. 2 shows the main internal structure of the optical semiconductor device according to the embodiment. FIG. 2 shows a cross section of the optical semiconductor device as seen from a plane along line I-I in FIG. 1 (z-x plane).

FIG. 3 primarily shows a moisture-proof structure of the optical semiconductor device according to the embodiment as seen from the z-x plane that is the same as the plane from which FIG. 2 is seen.

FIGS. 4A and 4B show a main step of a method for producing the optical semiconductor device according to the embodiment. FIG. 4A shows a product as seen from the x-y plane that is the same as the plane from which FIG. 1 is seen. FIG. 4B shows the product shown in FIG. 4A as seen from the z-x plane that is the same as the plane from which FIG. 2 is seen.

FIGS. 5A and 5B show a main step of the method for producing the optical semiconductor device according to the embodiment. FIG. 5A shows a product as seen from the x-y plane. FIG. 5B shows the product shown in FIG. 5A as seen from the z-x plane.

FIG. 6 shows a main step of the method for producing the optical semiconductor device according to the embodiment. FIG. 6 shows a product as seen from the z-x plane.

FIGS. 7A and 7B show a main step of the method for producing the optical semiconductor device according to the embodiment. FIG. 7A shows a product as seen from the x-y plane. FIG. 7B shows the product shown in FIG. 7A as seen from the z-x plane.

FIGS. 8A and 8B show a main step of the method for producing the optical semiconductor device according to the embodiment. FIG. 8A shows a product as seen from the x-y plane. FIG. 8B shows the product shown in FIG. 8A as seen from the z-x plane.

FIGS. 9A and 9B show a main step of the method for producing the optical semiconductor device according to the embodiment. FIG. 9A shows a product as seen from the x-y plane. FIG. 9B shows the product shown in FIG. 9A as seen from the z-x plane.

FIGS. 10A and 10B show a main step of the method for producing the optical semiconductor device according to the embodiment, and show a product as seen from the z-x plane.

FIG. 11 shows a main step of the method for producing the optical semiconductor device according to the embodiment, and shows a product as seen from the z-x plane.

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FIG. 12 shows a main step of the method for producing the optical semiconductor device according to another embodiment, and shows a product as seen from the z-x plane.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

Description of Embodiments of Invention

First, some embodiments according to the present invention will be described. A method for producing an optical assembly according to a first aspect of the present invention includes the steps of forming an optical semiconductor device having a first principal surface and a first back surface opposite to the first principal surface, the optical semiconductor device including a substrate, a recess formed on the first principal surface, and an first optical waveguide formed on the substrate, the recess having a first center axis substantially orthogonal to the first principal surface; forming an optical waveguide device having a second principal surface and a second back surface opposite to the second principal surface, the optical waveguide device including a through-hole having a second center axis substantially orthogonal to the second back surface, and a second optical waveguide, the through-hole penetrating through the second principal surface and the second back surface; positioning the optical semiconductor device and the optical waveguide device so that the first principal surface and the second back surface face each other; aligning the optical semiconductor device and the optical waveguide device by inserting a guide pin into the through-hole and the recess, the first center axis of the recess and the second center axis of the through-hole being aligned with each other; and joining the optical semiconductor device and the optical waveguide device to each other. The recess is extended from the first principal surface to a middle portion of the substrate. In addition, in the step of aligning the optical semiconductor device and the optical waveguide device, the first optical waveguide of the optical semiconductor device is optically coupled with the second optical waveguide of the optical waveguide device.

In the method for producing an optical assembly, the first optical waveguide of the optical semiconductor device and the second optical waveguide of the optical waveguide device are easily and precisely aligned with each other by inserting the guide pin into the through-hole of the optical waveguide device and the recess of the optical semiconductor device. Accordingly, the first optical waveguide of the optical semiconductor device is optically coupled with the second optical waveguide of the optical waveguide device with high efficiency. Therefore, in order to optically couple the first optical waveguide of the optical semiconductor device and the second optical waveguide of the optical waveguide device with each other, a process of precisely aligning the positions of the optical semiconductor device and the optical waveguide device is not required. By inserting the guide pin into the through-hole of the optical waveguide device and the recess of the optical semiconductor device, the optical semiconductor device and the optical waveguide device are quickly aligned with each other.

In the method for producing an optical assembly according to the invention, preferably, the recess includes a first region and a second region arranged adjacent to the first region. The first region has an opening at the first principal surface and a taper portion whose diameter increases from a boundary surface between the first region and the second region towards the first principal surface, the boundary

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surface being disposed in the substrate. The second region has a first end portion of the recess in the substrate and a taper portion whose diameter decreases from the boundary surface towards the first end portion. The guide pin includes a second end portion that has an end surface and a taper portion whose diameter decreases towards the end surface. The taper portion of the first region has a taper ratio greater than a taper ratio of the taper portion of the second end portion. In addition, the taper ratio of the taper portion of the second end portion is greater than a taper ratio of the taper portion of the second region. Furthermore, in the step of aligning the optical semiconductor device and the optical waveguide device by inserting the guide pin into the through-hole and the recess, the guide pin may be in contact with the through-hole, and the second end portion of the guide pin may be in contact with the recess at the boundary surface.

By inserting the tapered-shape end portion (second end portion) of the guide pin into the recess of the optical semiconductor device, the guide pin may be in contact with a side wall of the recess, uniformly and closely. Therefore, even if diameter dimension of the recess varies, it is possible to align the center axis of the recess and the center axis of the guide pin with a relatively high precision. Specifically, the guide pin is in contact with the recess at the boundary surface between the first region and the second region. In addition, the boundary surface is formed in the substrate. Therefore, the guide pin is inserted into the recess so as to be in contact with the side wall of the recess in the substrate which has a relatively high rigidity. Consequently, cracking caused by the contact of the guide pin and the side wall of the recess with each other may be suppressed. Occurrence of crystal defect caused by the cracking may be also suppressed. In addition, even if the cracking occurs in the substrate by the contact between the guide pin and the side wall of the recess, the cracking in the substrate does not increase because the substrate has a relatively high rigidity.

In the method for producing an optical assembly according to the invention, the optical semiconductor device may further include an electric wiring structure formed on the substrate. The electric wiring structure may include an electric wiring section and a moisture-proof structure. In addition, the moisture-proof structure may be formed between the electric wiring section and the recess so as to surround the recess.

The moisture-proof structure is provided between the electric wiring section and the recess and surrounds the recess. Therefore, the moisture-proof structure intercepts moisture that enters into the optical semiconductor device from a side surface of the recess. Therefore, with the moisture-proof structure, oxidation corrosion of the electric wiring section in the electric wiring structure is prevented.

In the method for producing an optical assembly according to the invention, preferably, the moisture-proof structure includes a metallic layer that is the same as that of the electric wiring section.

In the method for producing an optical assembly according to the invention, preferably, the optical semiconductor device includes a plurality of recesses. The optical waveguide device includes a plurality of through-holes. In addition, the optical semiconductor device and the optical waveguide device are aligned by inserting each of the guide pins into one of through-holes and one of the recesses.

In the method for producing an optical assembly according to the invention, preferably, the optical semiconductor device and the optical waveguide device are joined to each

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other using resin or solder while the guide pin is inserted in the through-hole and the recess.

A method for producing an optical assembly according to a second aspect of the present invention includes the steps of forming an optical semiconductor device having a first principal surface and a first back surface opposite to the first principal surface, the optical semiconductor device including a substrate, a recess formed on the first principal surface, and an first optical waveguide formed on the substrate, the recess having a first center axis substantially orthogonal to the first principal surface; forming an optical waveguide device having a second principal surface and a second back surface opposite to the second principal surface, the optical waveguide device including a through-hole having a second center axis substantially orthogonal to the second back surface, and a second optical waveguide, the through-hole penetrating through the second principal surface and the second back surface; inserting a guide pin into the recess of the optical semiconductor device; positioning the optical semiconductor device and the optical waveguide device so that the first principal surface and the second back surface face each other by sliding the optical waveguide device while the guide pin is fitted into the through-hole of the optical waveguide device, the first center axis of the recess and the second center axis of the through-hole being aligned with each other; and joining the optical semiconductor device and the optical waveguide device to each other. The recess is extended from the first principal surface to a middle portion of the substrate. In addition, in the step of positioning the optical semiconductor device and the optical waveguide device, the first optical waveguide of the optical semiconductor device is optically coupled with the second optical waveguide of the optical waveguide device.

In the method for producing an optical assembly, the first optical waveguide of the optical semiconductor device and the second optical waveguide of the optical waveguide device are easily and precisely aligned with each other by using the guide pins. Accordingly, the first optical waveguide of the optical semiconductor device is optically coupled with the second optical waveguide of the optical waveguide device with high efficiency. In the method, first, the guide pin is inserted into the recess of the optical semiconductor device. Thereafter, the optical waveguide device is slid while the guide pin is fitted into the through-hole of the optical waveguide device. Therefore, before inserting the guide pin into the through-hole and the recess, the step of positioning the optical semiconductor device and the optical waveguide device so as to roughly align the center axis of the recess and the center axis of the through-hole with each other may be omitted.

An optical assembly according to a third aspect of the present invention includes an optical semiconductor device including a substrate, a recess formed on a principal surface thereof, and an first optical waveguide formed on the substrate, the recess having a first center axis substantially orthogonal to the principal surface and extending from the principal surface to a middle portion of the substrate; an optical waveguide device provided on the principal surface of the optical semiconductor device, the optical waveguide device including a through-hole having a second center axis substantially orthogonal to the principal surface and a second optical waveguide, the through-hole penetrating through the optical waveguide device in a direction substantially orthogonal to the principal surface; and a guide pin inserting into the recess and the through-hole, the guide pin having a third center axis substantially orthogonal to the principal surface. The first center axis of the recess is aligned with the

second center axis of the through-hole. The third center axis of the guide pin is aligned with the first center axis and the second center axis. In addition, the first optical waveguide of the optical semiconductor device and the second optical waveguide of the optical waveguide device are optically coupled with each other.

According to the optical assembly, the first optical waveguide of the optical semiconductor device and the second optical waveguide of the optical waveguide device are easily and precisely aligned with each other by inserting the guide pin into the through-hole of the optical waveguide device and the recess of the optical semiconductor device. Accordingly, the first optical waveguide of the optical semiconductor device is optically coupled with the second optical waveguide of the optical waveguide device with high efficiency.

In the optical assembly according to the invention, preferably, the recess includes a first region and a second region arranged adjacent to the first region. The first region has an opening at the principal surface and a taper portion whose diameter increases from a boundary surface between the first region and the second region towards the principal surface, the boundary surface being disposed in the substrate. The second region has a first end portion of the recess in the substrate and a taper portion whose diameter decreases from the boundary surface towards the first end portion. The guide pin includes a second end portion that has an end surface and a taper portion whose diameter decreases towards the end surface. The taper portion of the first region has a taper ratio greater than a taper ratio of the taper portion of the second end portion. In addition, the taper ratio of the taper portion of the second end portion is greater than a taper ratio of the taper portion of the second region. Furthermore, the guide pin may be in contact with the through-hole, and the second end portion of the guide pin may be in contact with the recess at the boundary surface.

By inserting the tapered-shape end portion (second end portion) of the guide pin into the recess of the optical semiconductor device, the guide pin may be in contact with a side wall of the recess, uniformly and closely. Therefore, even if diameter dimension of the recess varies, it is possible to align the center axis of the recess and the center axis of the guide pin with a relatively high precision. Specifically, the guide pin is in contact with the recess at the boundary surface between the first region and the second region. In addition, the boundary surface is formed in the substrate. Therefore, the guide pin is inserted into the recess so as to be in contact with the side wall of the recess in the substrate which has a relatively high rigidity. Consequently, cracking caused by the contact of the guide pin and the side wall of the recess with each other may be suppressed. Occurrence of crystal defect caused by the cracking may be also suppressed. In addition, even if the cracking occurs in the substrate by the contact between the guide pin and the side wall of the recess, the cracking in the substrate does not increase because the substrate has a relatively high rigidity.

In the optical assembly according to the invention, preferably, the optical semiconductor device further includes an electric wiring structure formed on the substrate. The electric wiring structure includes an electric wiring section and a moisture-proof structure. In addition, the moisture-proof structure is formed between the electric wiring section and the recess so as to surround the recess.

The moisture-proof structure is provided between the electric wiring section and the recess and surrounds the recess. Therefore, the moisture-proof structure intercepts moisture that enters into the optical semiconductor device

from a side surface of the recess. Therefore, with the moisture-proof structure, oxidation corrosion of the electric wiring section in the electric wiring structure is prevented.

In the optical assembly according to the invention, preferably, the moisture-proof structure includes a metallic layer that is the same as that of the electric wiring section.

Detail of Embodiments of the Invention

Next, some embodiments will be described in detail as referring to drawings. In describing the drawings, if possible, corresponding portions are given the same reference numerals and the same descriptions thereof are not given. A structure of an optical assembly 100 according to an embodiment is described with reference to FIGS. 1, 2, and 3. FIG. 1 shows an orthogonal coordinate system that is defined by an x axis, a y axis, and a z axis. The orthogonal coordinate system shown in FIG. 1 is the same as those shown in FIGS. 2 to 11. FIG. 1 is a perspective plan view (in an x-y plane) of an internal structure of an optical semiconductor device 1. FIG. 2 shows an internal structure of the optical assembly 100 as seen from a plane along line I-I in FIG. 1 (z-x plane). FIG. 3 primarily shows a moisture-proof 5c1 of the optical assembly 100 as seen from a plane that is the same as the plane (z-x plane) from which FIG. 2 is seen. The optical assembly 100 includes the optical semiconductor device 1, an optical waveguide device 90, two guide pins TP, and a joint 40. The optical semiconductor device 1 and the optical waveguide device 90 are joined to each other through the joint 40. The joint 40 is made of, for example, resin or solder.

The optical semiconductor device 1 includes a substrate 2, an oxide film 3, an optical waveguide unit 4, an electric wiring structure 5, two recesses Ha, a principal surface Sf1a, and a back surface Sf1b. The principal surface Sf1a and the back surface Sf1b both extend along the x-y plane. The principal surface Sf1a is positioned on the side opposite to the back surface Sf1b. The oxide film 3 is provided on the substrate 2. The optical waveguide unit 4 is provided on the oxide film 3. The electric wiring structure 5 is provided on the optical waveguide unit 4. The back surface Sf1b, the substrate 2, the oxide film 3, the optical waveguide unit 4, the electric wiring structure 5, and the principal surface Sf1a are disposed in that order in the direction of the z axis. The oxide film 3 is in contact with the substrate 2. The optical waveguide unit 4 is in contact with the oxide film 3. The electric wiring structure 5 is in contact with the optical waveguide unit 4. The substrate 2 has a back surface 2b which is disposed opposite to a boundary surface between the substrate 2 and the oxide film 3. The back surface 2b of the substrate 2 corresponds to the back surface Sf1b of the optical semiconductor device 10. The electric wiring structure 5 has a top surface which is disposed opposite to a boundary surface between the electric wiring structure 5 and the optical waveguide unit 4. The top surface of the electric wiring structure 5 corresponds to the principal surface Sf1a of the optical semiconductor device 1.

The optical waveguide unit 4 includes an optical device unit. The optical device unit of the optical waveguide unit 4 includes an optical connecting unit 42, an optical waveguide 4c1, an optical waveguide 4c2, and an optical modulator 4d. In the embodiment, the optical device unit includes two optical modulators as shown in FIG. 1. The optical connecting unit 42 includes a light output portion 4a and a light input portion 4b. Each of the light output portion 4a and the light input portion 4b includes a grating coupler having a diffraction grating structure. The light output portion 4a

includes an optical waveguide **1a**, and the light input portion **4b** includes an optical waveguide **1b**. The optical waveguide **1a** and the optical waveguide **1b** extend in the direction of the *z* axis.

The optical modulator **4d** is a Mach-Zehnder modulator (MZM). The optical modulator **4d** includes two modulation arms **4d1**, a 1×2 multi-mode interface (MMI) coupler **4d2**, and a 1×2 multi-mode interface (MMI) coupler **4d3**. The two modulation arms **4d1** are disposed parallel to each other. One end of each optical waveguide **4c1** and an end of each of the two modulation arms **4d1** are optically coupled to the 1×2 MMI coupler **4d2**. The other end of each optical waveguide **4c1** is optically coupled to its corresponding light output portion **4a**. One end of each optical waveguide **4c2** and the other end of each of the two modulation arms **4d1** are optically coupled to the 1×2 MMI coupler **4d3**. The other end of each optical waveguide **4c2** is connected to its corresponding light input portion **4b**. The two modulation arms **4d1** of the optical modulator **4d** extend between the 1×2 MMI coupler **4d2** and the 1×2 MMI coupler **4d3**.

The optical waveguide **4c1**, the optical waveguide **4c2**, the 1×2 MMI coupler **4d2**, and the 1×2 MMI coupler **4d3** have a rectangular cross section (defined by a plane that is perpendicular to the principal surface **Sf1a**). The modulation arm **4d1** has a ridge cross section (defined by the plane that is perpendicular to the principal surface **Sf1a**). The optical device unit of the optical waveguide unit **4** is embedded in a film formed of the same material (such as silicon oxide (SiO_2)) as the electric wiring structure **5**.

The modulation arm **4d1** includes an n-type region **4d11** and a p-type region **4d12**. The n-type region **4d11** and the p-type region **4d12** of the modulation arm **4d1** extend from the 1×2 MMI coupler **4d2** towards the 1×2 MMI coupler **4d3** (direction of the *x* axis). The n-type region **4d11** and the p-type region **4d12** of the modulation arm **4d1** are in contact with each other. By applying a voltage between the n-type region **4d11** and the p-type region **4d12** of the modulation arm **4d1**, it is possible to modulate light passing through the modulation arm **4d1** because the effective refractive index of the modulation arm **4d1** changes depending on the applied voltage. By changing the effective refractive index of the modulation arm **4d1** of the optical modulator **4d**, phase of light passing through the modulation arm **4d1** is modulated depending on the applied voltage. Light passing through each of the modulation arms **4d1** enters into the 1×2 MMI coupler **4d3**, and is coupled to each other at the 1×2 MMI coupler **4d3**. In this case, the intensity of light output from the 1×2 MMI coupler **4d3** is modulated depending on the applied voltage.

The light output portion **4a** and the light input portion **4b** have a rectangular cross section. The light output portion **4a** and the light input portion **4b** may have a ridge waveguide structure. The light output portion **4a** and the light input portion **4b** are each provided with a grating. The gratings have periodic projections and recesses along a direction of propagation of light. The period of the grating is set, for example, on the order of the wavelength of light propagating in the waveguides **4c1** and **4c2** (that is, on the order of a value (λ_0/n_e) that is obtained by dividing a wavelength λ_0 in a vacuum by an effective refractive index n_e). By using the grating structure of the light output portion **4a**, the light propagating through the optical waveguide **4c1** is output to the outside from the light output portion **4a** through the principal surface **Sf1a** of the optical semiconductor device **1**. Alternatively, by using the grating structure of the light input portion **4b**, light that is incident upon the light input portion

4b from the outside through the principal surface **Sf1a** is coupled to the optical waveguide **4c2**.

The electric wiring structure **5** includes a first layer **51a**, a second layer **51b** and a third layer **51c**. The first layer **51a**, the second layer **51b**, and the third layer **51c** each include an insulating film formed of the same material (insulating film of the electric wiring structure **5**). The first layer **51a** is formed on the optical waveguide unit **4**. The second layer **51b** is formed on the first layer **51a**. The third layer **51c** is formed on the second layer **51b**. The first layer **51a**, the second layer **51b**, and the third layer **51c** are disposed in that order in the direction of the *z* axis. The first layer **51a** is in contact with the optical waveguide unit **4**. The second layer **51b** is in contact with the first layer **51a**. The third layer **51c** is in contact with the second layer **51b**. The electric wiring structure **5** also includes an electric wiring section **5a**, a moisture-proof structure **5b**, and a moisture-proof structure **5c1**. The electric wiring section **5a**, the moisture-proof structure **5b**, and the moisture-proof structure **5c1** are embedded in the insulating film of the electric wiring structure **5**. The electric wiring section **5a**, the moisture-proof structure **5b**, and the moisture-proof structure **5c1** include a metal layer. The electric wiring section **5a**, the moisture-proof structure **5b**, and the moisture-proof structure **5c1** each have a multilayer structure extending from the first layer **51a** to the third layer **51c** through the second layer **51b**.

In the embodiment, the electric wiring section **5a** includes a total of eight electric wires for applying voltage to the four n-type regions **4d11** and the four p-type regions **4d12**. The eight electric wires are electrically connected to the four n-type regions **4d11** and the four p-type regions **4d12** through plugs (not shown) provided at the first layer **51a** along the four n-type regions **4d11** and the four p-type regions **4d12**. The electric wiring section **5a** includes a conductor pattern **5a1**, a plug **5a2**, and a conductor pattern **5a3**. The plug **5a2** is disposed between the conductor pattern **5a1** and the conductor pattern **5a3**, and is electrically connected to the conductor pattern **5a1** and the conductor pattern **5a3**. The conductor pattern **5a1** and the conductor pattern **5a3** are electrically connected to each other through the plug **5a2**. The conductor pattern **5a1** and the plug **5a2** are provided in the second layer **51b**. The conductor pattern **5a3** is provided in the third layer **51c**. The conductor pattern **5a3** covers the insulating layer of the third layer **51c**. An opening portion **5a4** of the third layer **51c** is provided in part of a surface of the conductive pattern **5a3**. The conductor pattern **5a3** that is exposed through the opening portion **5a4** functions as a bonding pad.

The moisture-proof structure **5b** is provided along an outer periphery of the optical semiconductor device **1**. The moisture-proof structure **5b** is embedded in the insulating film of the electric wiring structure **5**. In plan view (in the *x-y* plane), the moisture proof structure **5b** surrounds the optical device unit of the optical waveguide unit **4** and the electric wiring section **5a**. The moisture-proof structure **5b** is capable of intercepting moisture that permeates the optical semiconductor device from a side surface of the outer periphery of the optical semiconductor device **1**. Therefore, with the moisture-proof structure **5b**, oxidation corrosion of the electric wiring section **5a** in the electric wiring structure **5** is prevented.

The moisture-proof structure **5b** includes a plug **5b1**, a conductor pattern **5b2**, a plug **5b3**, and a conductor pattern **5b4**. The plug **5b1**, the conductor pattern **5b2**, the plug **5b3**, and the conductor pattern **5b4** are disposed in that order from the first layer **51a** to the third layer **51c** (that is, in the

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direction of the z axis). The plug **5b1** is connected to the conductor pattern **5b2**. The plug **5b3** is connected to the conductor pattern **5b2** and the conductor pattern **5b4**. The plug **5b1** and the conductor pattern **5b4** are connected to each other through the conductor pattern **5b2** and the plug **5b3**. The plug **5b1** is provided in the first layer **51a**. The conductor pattern **5b2** and the plug **5b3** are provided in the second layer **51b**. The conductor pattern **5b4** is provided in the third layer **51c**. The conductor pattern **5b4** is covered by the insulating film of the third layer **51c**.

The moisture-proof structure **5c1** is provided on the substrate **2**. The moisture-proof structure **5c1** is embedded in the insulating film of the electric wiring structure **5**. In plan view (that is, in the x-y plane), the moisture-proof structure **5c1** is provided between the electric wiring section **5a** and a recess **Ha**. In plan view (in the x-y plane), the moisture-proof structure **5c1** surrounds the recesses **Ha**. The moisture-proof structure **5c1** intercepts moisture that permeates the optical semiconductor device from a side surface of its corresponding recess **Ha**. With the moisture-proof structure **5c1**, oxidation corrosion of the electric wiring section **5a** in the electric wiring structure **5** is prevented. That is, in plan view (in the x-y plane), the electric wiring section **5a** of the electric wiring structure **5** is surrounded by the moisture-proof structure **5b** and the moisture-proof structure **5c1**. Therefore, it is possible not only to intercept moisture that permeates the optical semiconductor device from a side surface of the outer periphery of the optical semiconductor device **1**, but also to intercept moisture that permeates the optical semiconductor device from a side surface of the recess **Ha**.

As shown in FIG. 3, the moisture-proof structure **5c1** includes a plug **5c11**, a conductor pattern **5c12**, a plug **5c13**, and a conductor pattern **5c14**. The plug **5c11**, the conductor pattern **5c12**, the plug **5c13**, and the conductor pattern **5c14** are disposed in that order (in the direction of the z axis) from the first layer **51a** towards the third layer **51c**. The plug **5c11** is connected to the conductor pattern **5c12**. The plug **5c13** is connected to the conductor pattern **5c12** and the conductor pattern **5c14**. The plug **5c11** and the conductor pattern **5c14** are connected to each other through the conductor pattern **5c12** and the plug **5c13**. The plug **5c11** is provided in the first layer **51a**. The conductor pattern **5c12** and the plug **5c13** are provided in the second layer **51b**. The conductor pattern **5c14** is provided in the third layer **51c**. The conductor pattern **5c14** is embedded in the insulating film of the third layer **51c**.

A recess **Ha** is provided for fitting a guide pin **TP**. In the embodiment, the two recesses **Ha** are provided for fitting each of the guide pins **TP**. The recess **Ha** is provided in the principal surface **Sf1a**. The recess **Ha** extends from the principal surface **Sf1a** to the substrate **2**. Center axis **Ha4** of the recess **Ha** is substantially orthogonal to the principal surface **Sf1a**.

The recess **Ha** includes a first region **Ha1** and a second region **Ha2** adjacent to the first region **Ha1**. The first region **Ha1** and the second region **Ha2** of the recess **Ha** are disposed in that order from the principal surface **Sf1a** to the back surface **Sf1b**. The second region **Ha2** is extended to the middle portion of the substrate **2**, and includes an end portion **Ed1** of the recess **Ha** in the substrate **2**. An opening **Op** is formed at the principal surface **Sf1a** in the position corresponding to the first region **Ha1** of the recess **Ha**. In the embodiment, a boundary surface **K1** between the first region **Ha1** and the second region **Ha2** is positioned in the substrate **2**. The first region **Ha1** of the recess **Ha** has a taper portion in which the diameter of the first region **Ha1** increases

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towards a principal surface **2a** of the substrate **2** from the boundary surface **K1** between the first region **Ha1** and the second region **Ha2**. The first region **Ha1** of the recess **Ha** has a uniform diameter from the principal surface **2a** towards the principal surface **Sf1a**. The second region **Ha2** of the recess **Ha** has a taper portion whose diameter decreases from the boundary surface **K1** towards the end portion **Ed1**. The guide pin **TP** includes an end portion **Ed2** with an end surface **Es**. The end portion **Ed2** of the guide pin **TP** has a taper portion whose diameter decreases towards the end surface **Es** of the end portion **Ed2**. The taper portion of the first region **Ha1** has a taper ratio that is larger than that of the taper portion of the end portion **Ed2** of the guide pin **TP**. The taper portion of the end portion **Ed2** has a taper ratio that is larger than that of the taper portion of the second region **Ha2**. The guide pin **TP** is in contact with a wall of a through-hole **91c** of a base **91** of the optical waveguide device **90** (The through-hole **91c** of the base **91** will be described later). The end portion **Ed2** of the guide pin **TP** is in contact with a wall of the recess **Ha** at the boundary surface **K1**. Here, the term "taper ratio" is defined as a value that is obtained by dividing the difference between a maximum diameter and a minimum diameter at the tapering region, in which the diameter changes due to the tapered shape, by the length of the tapering region.

The optical waveguide device **90** includes a base **91** and an optical waveguide **92**. The optical waveguide device **90** is provided on the principal surface **Sf1a** of the optical semiconductor device **1**. The base **91** is provided on the principal surface **Sf1a**. The optical waveguide **92** is provided on the base **91**. The base **91** includes an optical waveguide section **911**, a through-hole **91c**, a principal surface **Sf2a**, and a back surface **Sf2b**. In the embodiment, two through-holes **91c** are formed in the base **91**. The principal surface **Sf2a** and the back surface **Sf2b** extend along the x-y plane. The back surface **Sf2b** of the base **91** is arranged so as to face the principal surface **Sf1a** of the optical semiconductor device **1**. The optical waveguide **92** is provided on the principal surface **Sf2a** of the base **91**.

The through-holes **91c** are provided for inserting the respective guide pins **TP** therein. The two through-holes **91c** extend through the back surface **Sf2b** of the base **91** from the principal surface **Sf2a** of the base **91** along the direction of the z axis.

The guide pin **TP**, the recess **Ha**, and the through-hole **91c** extend in the direction of the z axis that is substantially orthogonal to the principal surface **Sf1a**. The guide pin **TP** has a center axis **TP1**. The recess **Ha** has a center axis **Ha4**. The through-hole **91c** has a center axis **91c1**. The center axis **TP1** of the guide pin **TP**, the center axis **91c1** of the through-hole **91c**, and the center axis **Ha4** of the recess **Ha** are all provided along the direction of the z axis. In the embodiment, the two recesses **Ha** are connected with either one of the two through-holes **91c**. One guide pin **TP** is inserted into each pair of recess **Ha** and through-hole **91c** that are connected to each other. The center axis **Ha4** of the recess **Ha** and the center axis **91c1** of the through-hole **91c** are aligned with each other. The recess **Ha** is connected with the corresponding through-hole **91c** through the guide pin **TP**. The center axis **TP1** of the guide pin **TP** is also aligned with the center axis **Ha4** of the recess **Ha** and the center axis **91c1** of the through-hole **91c**.

The optical waveguide section **911** extends in the direction of the z axis from the principal surface **Sf2a** to the back surface **Sf2b**. The optical waveguide section **911** includes an output waveguide section **91a** and an input waveguide section **91b**. The optical waveguide **92** includes an output

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waveguide **92a** and an input waveguide **92b**. In addition, the output waveguide **92a** includes an optical waveguide **93a**, and the input waveguide **92b** includes an optical waveguide **93b**. The optical waveguide **93a** of the output waveguide **92a** is optically coupled to the output waveguide section **91a** of the optical waveguide section **911**. The optical waveguide **93b** of the input waveguide **92b** is optically coupled to the input waveguide section **91b** of the optical waveguide section **911**. The optical waveguides **93a** and **93b** extend in the direction of the *z* axis.

The optical waveguide **1a** of the optical semiconductor device **1** is optically coupled to the optical waveguide **93a** of the optical waveguide device **90** through the output waveguide section **91a**. The optical waveguide **1b** of the optical semiconductor device **1** are optically coupled to the optical waveguide **93b** of the optical waveguide device **90** through the input waveguide section **91b**. The optical waveguides **1a** and **1b** of the optical semiconductor device **1** also extend in the direction of the *z* axis.

As described above, the optical semiconductor device **1** and the optical waveguide device **90** are arranged so that the principal surface **Sf1a** and the back surface **Sf2b** face each other. Further, the optical semiconductor device **1** and the optical waveguide device **90** are arranged so that each of the center axes **Ha4** of the two recesses **Ha** is aligned with one of the center axes **91c1** of the through-holes **91c**. Still further, the optical waveguide **1a** and the optical waveguide **1b** of the optical semiconductor device **1** are optically coupled with the optical waveguide **93a** and the optical waveguide **93b** of the optical waveguide device **90**, respectively.

The substrate **2** is formed of Si. The substrate **2** has a thickness of about 725 μm . The oxide film **3** is made of, for example, silicon oxide (SiO_2). Hereinafter, the oxide film **3** will be denoted as the silicon oxide (SiO_2) film **3**. The silicon oxide (SiO_2) film **3** may be formed of a buried oxide (BOX) layer on the Si substrate **2**. The silicon oxide (SiO_2) film **3** has a thickness of about 2 μm . In the optical waveguide unit **4**, an Si optical device unit is embedded in a silicon oxide (SiO_2) layer. The optical device unit of the optical waveguide unit **4** includes the optical connecting unit **42**, the optical waveguide **4c1**, the optical waveguide **4c2**, and the optical modulator **4d**. The optical device unit of the optical waveguide unit **4** is made of Si. The optical waveguide unit **4** has a thickness of about 0.3 μm .

The first layer **51a**, the second layer **51b**, and the third layer **51c** are formed of an insulating film such as a silicon oxide (SiO_2) film. The first layer **51a** has a film thickness of about 300 nm. The second layer **51b** has a film thickness of about 1100 nm. The third layer **51c** has a film thickness of about 1300 nm.

The conductor pattern **5a1**, the conductor pattern **5b2**, and the conductor pattern **5c12** have a layered structure of TiN (50 nm)/Ti (10 nm)/AlCu (500 nm)/Ti (10 nm)/TiN (50 nm). The plug **5a2**, the plug **5b1**, the plug **5b3**, the plugs **5c11**, and the plugs **5c13** have a layered structure of Ti (30 nm)/TiN (100 nm)/W (800 nm). The conductor pattern **5a3**, the conductor pattern **5b4**, and the conductor pattern **5c14** have a layered structure of TiN (50 nm)/Ti (10 nm)/AlCu (800 nm).

The base **91** is formed of, for example, resin, such as polyphenylene sulfide resin. The resin of the base **91** may include a glass filler. The diameter of the through-hole **91c** in the base **91** is set to be $800\ \mu\text{m} \pm 1\ \mu\text{m}$, for example.

The taper ratio of the taper portion of the first region **Ha1** is approximately 0.22. The taper ratio of the taper portion of

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the second region **Ha2** is approximately 0.02. The taper ratio of the taper portion of the end portion **Ed2** of the guide pin TP is approximately 0.1.

The taper portion of the first region **Ha1** has a length of about 150 μm from the principal surface **2a** of the substrate **2** towards the back surface **Sf1b** of the substrate **2**. The second region **Ha2** of the recess **Ha** has a length of about 480 μm towards the back surface **Sf1b** from the boundary surface **K1** between the first region **Ha1** and the second region **Ha2** of the recess **Ha**. The boundary surface **K1** has a diameter of about 600 μm .

The guide pin TP may be formed by grinding a steel material made of SUS303 stainless steel using a centerless inked grinding method after machining the steel material using a numerical control (NC) lathe. The end portion **Ed2** of the guide pin TP has a taper portion. The end surface **Es** has a diameter of 0.560 to 0.595 mm. A portion of each guide pin TP excluding the tapering end portion **Ed2** has a diameter of $0.8\ \text{mm} \pm 0.001\ \text{mm}$, for example.

In the optical assembly **100** having the above-described structure, a fixing member such as resin or solder is filled into a gap between the optical semiconductor device **1** and the optical waveguide device **90** so as to fix the optical semiconductor device **1** and the optical waveguide device **90** (in particular, the base **91**), while the two guide pins TP are inserted into the optical waveguide device **90** and the optical semiconductor device **1**. Then, the fixing member is cured, and a cured fixing member becomes a joint **40** disposed between the optical semiconductor device **1** and the optical waveguide device **90** as shown in FIG. 2. The optical semiconductor device **1** and the optical waveguide device **90** are fixed by the joint **40** made of the cured fixing member. By inserting the guide pins TP into the recesses **Ha** of the optical semiconductor device **1** and the through-holes **91c** of the optical waveguide device **90**, respectively, the relative position between the optical semiconductor device **1** and the optical waveguide device **90** is precisely and easily determined. Therefore, in the embodiment, a process of precisely aligning the positions of the optical semiconductor device **1** and the optical waveguide device **90** is not required. After fixing the optical semiconductor device **1** and the optical waveguide device **90**, the guide pins TP may be removed from the optical semiconductor device **1** and the optical waveguide device **90**. Furthermore, after removing the guide pins TP from the optical semiconductor device **1** and the optical waveguide device **90**, the through-holes **91c** and the recesses **Ha** may be filled with resin or the like.

When the guide pin TP is inserted into the recess **Ha** of the optical semiconductor device **1**, the guide pin TP is uniformly abutted onto a side wall surface of the recess **Ha** because the guide pin TP has the tapering end portion **Ed2**. Therefore, the center axis **Ha4** of the recess **Ha** and the center axis TP are aligned with a high precision regardless of variations in the diameters of the recesses **Ha**. The side wall surface of the recess **Ha** is abutted to the guide pin TP at the boundary surface **K1** between the first region **Ha1** and the second region **Ha2**. The boundary surface **K1** exists in the substrate **2**. Therefore, the guide pin TP contacts the side wall surface of the corresponding recess **Ha** in the inside of the substrate **2** having a relatively high rigidity. As a result, cracking caused by contact of the guide pin TP with the side wall surface of the recess **Ha** is reduced. Crystal defects caused by the cracking are also suppressed. Even if cracking occurs in the substrate **2**, the cracking is stopped in the inside of the substrate **2** because the substrate **2** has a relatively high rigidity. Further, it is possible to prevent the cracks in

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the substrate 2 from reaching the optical waveguide unit 4 by the silicon oxide (SiO_2) film 3.

In the embodiment, the optical semiconductor device 1 includes a single moisture-proof structure 5b. The optical semiconductor device 1 may include a plurality of moisture-proof structures 5b. In such a case, in the optical semiconductor device 1, a moisture-proof structure 5b is provided at an inner side of another moisture-proof structure 5b in plan view (in the x-y plane).

In the embodiment, in the optical semiconductor device 1, a single moisture-proof structure 5c1 is provided around each of the recesses Ha. A plurality of moisture-proof structures 5c1 may be provided around each of the recesses Ha. In this case, in the optical semiconductor device 1, a moisture-proof structure 5c1 is provided at an inner side of another moisture-proof structure 5c1 in plan view (in the x-y plane).

In the embodiment, the optical semiconductor device 1 includes a single second layer 51b. The optical semiconductor device 1 may include a plurality of second layers 51b. In this case, the plurality of second layers 51b are stacked upon each other between the first layer 51a and the third layer 51c from the first layer 51a towards the third layer 51c (in the direction of the z axis).

In the embodiment, the optical semiconductor device 1 includes two sets of the guide pin TP, the recess Ha, and the through-hole 91c. The optical semiconductor device 1 may include three or more sets of the guide pin TP, the recess Ha, and the through-hole 91c.

In the embodiment, the optical assembly 100 has an optical signal output structure (the light output portion 4a, the output waveguide section 91a, and the output waveguide 92a) and an optical signal input structure (the light input portion 4b, the input waveguide section 91b, and the input waveguide 92b). The optical assembly 100 may include only one of the optical signal output structure and the optical signal input structure.

In the embodiment, the optical semiconductor device 1 includes two light output portions 4a and two light input portions 4b. The number of the light output portion 4a and the number of the light input portion 4b are independently adjustable. In this case, the numbers of the optical waveguide 4c1, the optical waveguide 4c2, the optical modulator 4d, the output waveguide section 91a, the input waveguide section 91b, the output waveguide 92a, and the input waveguide 92b may be set in accordance with the number of the light output portion 4a and the number of the light input portion 4b. In the embodiment, the optical waveguide 93a, the optical waveguide 93b, the optical waveguide 1a and the optical waveguide 1b extend in the direction of the z axis. The optical waveguide 93a, the optical waveguide 93b, the optical waveguide 1a, and the optical waveguide 1b may extend slantwise in the direction of the z axis. Even in this case, the optical waveguide 1a and the optical waveguide 1b are optically coupled with the optical waveguide 93a and the optical waveguide 93b, respectively.

First Example

With reference to FIG. 4A to FIG. 11, a method for producing the optical assembly 100 according to the embodiment is described. FIGS. 4A, 4B, 5A, 5B, 7A, 7B, 8A, 8C, 9A, and 9B show the main steps of the method for producing the optical assembly 100. FIGS. 4A, 5A, 7A, 8A, and 9A show a product as seen from a plane (x-y plane) that is the same as the plane from which FIG. 1 is seen. FIGS. 4B, 5B, 7B, 8B, and 9B show the product shown in FIGS.

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4A, 5A, 7A, 8A, and 9A as seen from a plane (z-x plane) that is the same as the plane from which FIG. 2 is seen. FIGS. 6, 10A, 10B, and 11 show a main step of the method for producing the optical assembly 100, and a product as seen from a plane (z-x plane) that is the same as the plane from which FIG. 2 is seen.

First, as shown in FIGS. 4A and 4B, an SOI substrate is provided. The SOI substrate includes a silicon (Si) substrate 21 (wafer), a silicon oxide (SiO_2) film 31 (BOX layer) formed on the Si substrate 21, and a silicon (Si) layer 41a formed on the silicon oxide film 31. The Si substrate has a thickness of about 725 μm . The silicon oxide film 31 has a thickness of about 2 μm . The Si layer 41a has a thickness of about 0.3 μm . In the Si layer 41a, an n-type region 4d11 and a p-type region 4d12 are formed so as to form an optical modulator 4d. The n-type region 4d11 is formed by ion implantation of phosphorous (P), and the p-type region 4d12 is formed by ion implantation of boron (B). After the ion implantation of phosphorous (P) and boron (B) into the Si layer 41a, an annealing process is performed on the ion-implanted wafer.

As shown in FIGS. 5A and 5B, the Si layer 41a is etched by using a resist mask (not shown) having a pattern of an optical device unit of an optical waveguide unit 4. After etching the Si layer 41a, the pattern is transferred to the Si layer 41a. As a result, a pattern of the Si layer 41a for forming the optical device unit is formed on the silicon oxide film 31. Then, the resist mask is removed. The pattern of the Si layer 41a for forming the optical device unit includes patterns for forming a light output portion 4a, a light input portion 4b, an optical waveguide 4c1, an optical waveguide 4c2, and an optical modulator 4d.

In the light output portion 4a and the light input portion 4b, grooves having a predetermined period are formed in the Si layer 41a so as to form a diffraction grating structure. The diffraction grating structure has a period on the order of a wavelength (λ) propagating through an optical waveguide, and has a depth of about 0.15 μm . Here, the wavelength (λ) propagating through the optical waveguide having an effective refractive index n_e is equal to a value (λ_0/n_e) obtained by dividing a wavelength λ_0 of light in a vacuum by the effective refractive index n_e . The optical modulator 4d is formed by etching the Si layer 41a so as to have a ridge structure having a height (etching depth) of about 0.2 μm . The optical waveguide 4c1, the 1x2 multi-mode interface (MMI) coupler 4d2, and the 1x2 multi-mode interface (MMI) coupler 4d3 have a rectangular cross section.

Next, as shown in FIG. 6, the optical device unit formed on the silicon oxide (SiO_2) film 31 is covered with silicon oxide (SiO_2) layer so as to form an optical waveguide unit 41b. Further, a silicon oxide (SiO_2) layer having a thickness of about 700 nm is formed on the optical waveguide unit 41b. Thereafter, by using chemical mechanical polishing (CMP) method, the silicon oxide (SiO_2) layer formed on the optical waveguide unit 41b is polished so as to have a flat surface. The polished silicon oxide (SiO_2) layer on the optical waveguide unit 41b has a thickness of about 300 nm. By these steps, a first layer 51a1 is formed.

Next, as shown in FIGS. 7A and 7B, the first layer 51a1 is etched by using a resist-mask (not shown) so as to form a plurality of openings through which a surface of the n-type region 4d11 and a surface of the p-type region 4d12 are exposed. A first metal layer is formed in the plurality of openings as an electrode. The first metal layer is in contact with the surface of n-type regions 4d11 and the surface of the p-type regions 4d12 through the plurality of openings. By this process, plugs 4d11a and plugs 4d12a are formed. When

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the first layer **51a1** is etched by using the resist-mask (not shown) to form the plurality of openings, grooves are simultaneously formed by etching the first layer **51a1** using the same resist-mask in a portion where a moisture-proof structure **5b** is formed and a portion where moisture-proof structures **5c1** are formed. In the embodiment, the moisture-proof structure **5b** is formed along an outer periphery of the first layer **51a1**. The moisture-proof structures **5c1** are formed surrounding portions R1 where recesses Ha are formed. By filling these grooves with the first metal layer, a plug **5b1** and plugs **5c11** are formed. In order to form the plugs **4d11a**, the plugs **4d12a**, the plug **5b1**, and the plugs **5c11**, the first metal layer including Ti (30 nm)/TiN (100 nm)/W (800 nm) is formed so as to cover the entire surface of the first layer **51a1**. And, thereafter, a part of the first metal layer other than a region where the plugs **4d11a**, the plugs **4d12a**, the plug **5b1**, and the plugs **5c11** are formed is partially and selectively removed by etching. In this way, a first layer **51a2** is formed by forming the plugs **4d11a**, the plugs **4d12a**, the plug **5b1**, and the plugs **5c11** with respect to the first layer **51a1**.

Next, as shown in FIGS. 8A and 8B, a second metal layer including TiN (50 nm)/Ti (10 nm)/AlCu (500 nm)/Ti (10 nm)/TiN (50 nm) is formed on the entire surface of the first layer **51a2**. Thereafter, the second metal layer is partially and selectively etched to form a conductor pattern **5b2**, a conductor pattern **5a1**, and a conductor pattern **5c12**. As a result, the conductor pattern **5b2**, the conductor pattern **5a1**, and the conductor pattern **5c12** are formed on the surface of the first layer **51a2**. Next, a silicon oxide (SiO₂) layer having a thickness of about 2 μm is formed on the surface of the first layer **51a2** so as to cover the conductor pattern **5b2**, the conductor pattern **5a1**, and the conductor pattern **5c12**. Thereafter, the surface of the silicon oxide (SiO₂) layer is polished by using CMP method so that the surface of the silicon oxide (SiO₂) layer is made flat. By polishing the silicon oxide (SiO₂) layer, the silicon oxide (SiO₂) layer on the conductor pattern **5b2**, the conductor pattern **5a1**, and the conductor pattern **5c12** has a thickness of about 500 nm. A portion of the silicon oxide (SiO₂) layer on the conductor pattern **5c12**, the conductor pattern **5a1**, and the conductor pattern **5c12** is etched to expose surfaces of the conductor pattern **5b2**, the conductor pattern **5a1**, and the conductor pattern **5c12**. As a result of this etching, openings of the silicon oxide (SiO₂) layer are formed on the conductor pattern **5b2**, the conductor pattern **5a1**, and the conductor pattern **5c12**. A third metal layer including Ti (30 nm)/TiN (100 nm)/W (800 nm) is formed in the openings so as to form a plug **5b3**, a plug **5a2**, and a plug **5c13**. In the step of forming the plug **5b3**, the plug **5a2**, and the plug **5c13**, the third metal layer including Ti (30 nm)/TiN (100 nm)/W (800 nm) is formed on the entire surface of the silicon oxide (SiO₂) layer and in the openings of the silicon oxide (SiO₂) layer formed on the first layer **51a2**. Thereafter, a part of the third metal layer formed on the surface of the silicon oxide (SiO₂) layer is partially and selectively etched so as to form the plug **5b3**, the plug **5a2**, and the plug **5c13**. In this way, a second layer **51b2** including the conductor pattern **5b2**, the conductor pattern **5a1**, the conductor pattern **5c12**, the plug **5b3**, the plug **5a2**, and the plug **5c13** is formed on the first layer **51a2**. When a plurality of second layers **51b** are to be provided, after forming the first layer **51a2**, the same step of forming the aforementioned second layer **51b2** is repeated for the number of second layers **51b**.

Next, a third layer **51c2**, which corresponds to a topmost layer, is formed. A fourth metal layer including TiN (50 nm)/Ti (10 nm)/AlCu (800 nm) is formed on the entire

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surface of the second layer **51b2**. Thereafter, the fourth metal layer is partially and selectively etched so as to form a conductor pattern **5b4**, a conductor pattern **5a3**, and a conductor pattern **5014** on the surface of the second layer **51b2**. Next, a silicon oxide (SiO₂) layer having a thickness of about 2 μm is formed on the second layer **51b2** so as to cover the conductor pattern **5b4**, the conductor pattern **5a3**, and the conductor pattern **5014**. Thereafter, the surface of the silicon oxide (SiO₂) layer is polished by using CMP method so that the surface of the silicon oxide (SiO₂) layer is made flat. By polishing the silicon oxide (SiO₂) layer, the silicon oxide (SiO₂) layer on the conductor pattern **5b4**, the conductor pattern **5a3**, and the conductor pattern **5014** has a thickness of about 500 nm. Further, the silicon oxide (SiO₂) layer on the conductor pattern **5a3** is etched to expose a surface of the conductor pattern **5a3** by using a resist mask. By the etching, an opening portion **5a4** having a square shape with dimensions of about 150 μm×150 μm is formed. By the above steps, the third layer **51c2** including the conductor pattern **5b4**, the conductor pattern **5a3**, the conductor pattern **5014**, and the opening portion **5a4** is formed. The thickness of the conductor pattern **5a3** is greater than the thickness of the conductor pattern **5a1** because the conductor pattern **5a3**, which is the topmost layer, is used as a bonding pad requiring a relatively high strength.

Next, as shown in FIGS. 9A and 9B, a surface of the third layer **51c2** is covered with a resist. Thereafter, a resist mask M1 having a circular opening pattern M1a is formed on the portion R1 where the recess Ha is formed using a photolithography technique. The circular opening pattern M1a has a diameter of 633 μm. Using the resist mask, the third layer **51c2**, the second layer **51b2**, the first layer **51a2**, the optical waveguide unit **41b**, the silicon oxide (SiO₂) film **31**, and the silicon (Si) substrate **21** are etched. As a result of this etching, the recess Ha is formed as shown in FIG. 10A. In the embodiment, the Si substrate **21** becomes a substrate **2**. The silicon oxide (SiO₂) film **31** becomes a silicon oxide (SiO₂) film **3**. The optical waveguide unit **41b** becomes an optical waveguide unit **4**. The first layer **51a2** becomes a first layer **51a**. The second layer **51b2** becomes a second layer **51b**. The third layer **51c2** becomes a third layer **51c**.

The step of forming the recess Ha is described in detail. First, the first region Ha1 is formed. In the first region Ha1, the substrate **21** made of silicon (Si) is etched by reactive ion etching (RIE) using an inductively coupled plasma (ICP) etching apparatus. The ICP etching apparatus includes a vacuum chamber, a high-frequency power source (ICP power source), and a high-frequency power source (Bias power source). The vacuum chamber includes a lower electrode and an upper electrode facing the lower electrode. The upper electrode is grounded. The substrate (wafer) is disposed on the lower electrode. The Bias power source is connected to the lower electrode so as to bias the substrate by supplying a Bias power to the lower electrode. The lower electrode has a cooling mechanism, which can cool the substrate. In addition, an induction coil is disposed on the side face of the vacuum chamber. The ICP power source is connected to the induction coil, and a high-frequency power (ICP power) is supplied to the induction coil so as to generate the ICP plasma. The conditions for the etching are as follows. The unit of sccm (i.e., standard cubic centimeters per minute) represents the flow rate at 25° C. under 1 atm, and the conditions are converted based on 1 sccm=1.69×10⁻⁴ Pa·m³·sec⁻¹. As an etching gas, gas mixture containing SF₆ gas, O₂ gas, and Ar gas is used. The flow rates of the SF₆ gas, O₂ gas, and Ar gas are 84 sccm, 67 sccm, and 59 sccm, respectively. The temperature of the substrate is 30° C., the

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IC power is 700 W, the Bias power is 30 W, and the pressure in the vacuum chamber is 4.0 Pa (30 mTorr).

In the embodiment, an etching time is set to be about 37 minutes and 30 seconds. By this etching, the substrate **21** is etched so that a taper ratio of about 0.22 and a depth of about 150 μm are realized, thereby forming the first region **Ha1**. The diameter of a bottom portion of the first region **Ha1** (diameter at the boundary surface **K1**) is about 600 μm .

Next, a second region **Ha1** is formed by using a so-called Bosch technology. First, using C_4F_8 gas as a reactive gas, a protective layer is formed on a top surface and a side surface defining a through-hole. The protective layer is made of a polymer whose main component is polytetrafluoroethylene. The conditions for forming the protective layer are as follows. The flow rate of the C_4F_8 gas is 85 sccm. The temperature of the substrate is 10° C., the IC power is 600 W, and the pressure in the vacuum chamber is 2.27 Pa (17 mTorr). The reaction time for forming the protective layer is about 5 seconds. Then, using a gas mixture containing SF_6 gas and O_2 gas as an etching gas, the substrate **21** is etched. The conditions of this etching of the substrate **21** are as follows. When the flow rate of SF_6 gas is, for example, 130 sccm, the flow rate of the O_2 gas is set to be 13 sccm. The temperature of the substrate is 10° C., the ICP power is 600 W, and the Bias power is 20 W. The pressure in the vacuum chamber is 3.47 (Pa) (26 mTorr). The etching time is set to be about 6 seconds. The above-described step of forming a protective layer and the step of etching performed after the step of forming a protective layer are repeated for approximately 137 minutes. By the above-described steps, the substrate **21** is etched so that a taper ratio on the order of 0.02 and a depth on the order of 480 μm (total depth of the **Ha2** is equal to 630 μm) are realized, thereby forming the second region **Ha2**.

In the steps of forming the first region **Ha1** and the second region **Ha2** of the recess **Ha**, the substrate **21** is isotropically etched by the RIE method using the ICP etching apparatus. Therefore, the circular opening pattern **M1a** of the resist mask **M1** is precisely transferred to patterns of the first region **Ha1** and the second region **Ha2** of the recess **Ha**. The center of the recess **Ha** is maintained at the same position as the center of the circular opening pattern **M1a** of the resist mask **M1**. Therefore, a center axis **Ha4** having a relatively high positional precision is provided.

Next, as shown in FIG. 10B, the resist mask **M1** is removed. After removing the resist mask **M1**, the substrate (wafer) is separated into a plurality of optical semiconductor devices **1** by dicing. Then, a previously produced optical waveguide device **90** and the optical semiconductor device **1** produced as mentioned above are prepared (hereunder, referred to as a first step).

After the first step, in a second step, the optical semiconductor device **1** and the optical waveguide device **90** are aligned so that an optical waveguide **1a** of the optical semiconductor device **1** is optically coupled with an optical waveguide **93a** of the optical waveguide device **90**, and so that an optical waveguide **1b** of the optical semiconductor device **1** is optically coupled with an optical waveguide **93b** of the optical waveguide device **90**.

In the second step, the optical semiconductor device **1** and the optical waveguide device **90** are disposed so that a principal surface **Sf1a** and a back surface **Sf2b** face each other. The optical semiconductor device **1** and the optical waveguide device **90** are positioned so that each of the center axes **Ha4** of the recesses **Ha** is roughly aligned with each of the center axes **91c1** of the through-holes **91c**. In positioning between the optical semiconductor device **1** and

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the optical waveguide device **90**, high precision for the positioning is not required. Next, guide pins **TP** are inserted into the through-holes **91c** and the recesses **Ha**. This causes the optical semiconductor device **1** and the optical waveguide device **90** to be positioned, easily and accurately. When the guide pins **TP** are inserted into the through-holes **91c** and the recesses **Ha**, each of the center axes **Ha4** of the recesses **Ha** is accurately aligned with each of the center axes **91c1** of the through-holes **91c**. In this case, each of the center axes **TP1** of the guide pins is also aligned with each of the center axes **Ha4** of the recesses **Ha** and each of the center axes **91c1** of the through-holes **91c**. The optical semiconductor device **1** and the optical waveguide device **90** are aligned with high precision by using the guide pins **TP**.

Next, in a third step, the optical semiconductor device **1** and the optical waveguide device **90** that have been positioned with a relatively high precision in the second step are joined to each other. In the third step, the optical semiconductor device **1** and the optical waveguide device **90** are joined to each other using a fixing member such as resin or solder (corresponding to the joint **40**) while the guide pins **TP** are inserted into the optical waveguide device **90** (in particular, the base **91**) and the optical semiconductor device **1**. The semiconductor device **1** and the optical waveguide device **90** are firmly fixed by the fixing member (joint **40**). In addition, the optical waveguide **1a** and the optical waveguide **1b** of the optical semiconductor device **1** are precisely aligned with the optical waveguide **93a** and the optical waveguide **93b** of the optical waveguide device **90**, respectively.

Second Example

With reference to FIG. 12, another method for producing the optical assembly **100** will be described below as a second example. FIG. 12 shows a main step of the method for producing the optical assembly **100** according to the embodiment, and a product as seen from a plane (z-x plane) that is the same as the plane from which FIG. 2 is seen.

As described above, in the second step of the first example, after positioning the optical semiconductor device **1** and the optical waveguide device **90** so as to roughly align the center axis **Ha4** of the recess **Ha** and the center axis **91c1** of the through-hole **91c** with each other, the guide pin **TP** is inserted into the through-hole **91c** and the recess **Ha**. By inserting the guide pin **TP** into the through-hole **91c** and the recess **Ha**, the center axis **Ha4** of the recess **Ha** is accurately aligned with the center axis **91c1** of the through-hole **91c**. As a result, the optical semiconductor device **1** and the optical waveguide device **90** are aligned with high precision by using the guide pin **TP**. In addition, the optical waveguide **1a** and the optical waveguide **1b** of the optical semiconductor device **1** are precisely aligned with the optical waveguide **93a** and the optical waveguide **93b** of the optical waveguide device **90**, respectively. The optical waveguide **1a** and the optical waveguide **1b** of the optical semiconductor device **1** are optically coupled with the optical waveguide **93a** and the optical waveguide **93b** of the optical waveguide device **90**, respectively.

In a second step of the second example, first, after the first step of forming the optical semiconductor device **1** and the optical waveguide device **90**, the guide pins **TP** are inserted into the recesses **Ha** of the optical semiconductor device **1** as shown in FIG. 12. Thereafter, the optical waveguide device **90** is slid while the guide pins **TP** are fitted into the through-holes **91c** of the optical waveguide device **90** so that the first principal surface and the second back surface face

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each other. The method for producing the optical assembly 100 other than the second step is substantially the same as that of the first example.

In the embodiment, first, the guide pins TP are inserted into the recesses Ha of the optical semiconductor device 1, after the first step of forming the optical semiconductor device 1 and the optical waveguide device 90. Each of the center axes TP1 of the guide pins is aligned with each of the center axes Ha4 of the recesses Ha. Thereafter, the optical semiconductor device 90 is slid while the guide pins TP are fitted into the through-holes 91c of the optical waveguide device 90 so that the first principal surface and the second back surface face each other. Each of the center axes Ha4 of the recesses Ha is accurately aligned with each of the center axes 91c1 of the through-holes 91c. As a result, the optical semiconductor device 1 and the optical waveguide device 90 are positioned, easily and accurately. In the embodiment, the optical waveguide 1a and the optical waveguide 1b of the optical semiconductor device 1 are precisely aligned with the optical waveguide 93a and the optical waveguide 93b of the optical waveguide device 90, respectively. In addition, before inserting the guide pin into the through-hole and the recess, the step of positioning the optical semiconductor device and the optical waveguide device so as to roughly align the center axis of the recess and the center axis of the through-hole with each other may be omitted.

Although the principles of the present invention have been illustrated and described in a preferred embodiment, it is understood by those skilled in the art that changes may be made in the present invention in terms of arrangements and details without departing from such principles. The present invention is not limited to the particular structures disclosed in the embodiment. Therefore, the right to make any changes and modifications on the basis of the scope of the claims and the scope of the spirit of the claims may be demanded.

What is claimed is:

1. A method for producing an optical assembly, comprising the steps of:

forming an optical semiconductor device having a first principal surface and a first back surface opposite to the first principal surface, the optical semiconductor device including a substrate, a recess formed in the first principal surface, and a first optical waveguide formed on the substrate, the recess having a first center axis substantially orthogonal to the first principal surface;

forming an optical waveguide device having a second principal surface and a second back surface opposite to the second principal surface, the optical waveguide device including a through-hole having a second center axis substantially orthogonal to the second back surface; and a second optical waveguide, the through-hole penetrating through the second principal surface and the second back surface;

positioning the optical semiconductor device and the optical waveguide device so that the first principal surface and the second back surface face each other; aligning the optical semiconductor device and the optical waveguide device by inserting a guide pin into the through-hole and the recess, the first center axis of the recess and the second center axis of the through-hole being aligned with each other; and

joining the optical semiconductor device and the optical waveguide device to each other, wherein

the recess extends from the first principal surface to an end portion in a middle portion of the substrate,

the recess includes a first region and a second region arranged adjacent to the first region,

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the first region has an opening at the first principal surface and a taper portion having a diameter that increases from a boundary surface between the first region and the second region towards the first principal surface, the boundary surface being in the substrate,

the second region has the end portion of the recess in the substrate and a taper portion having a diameter that decreases from the boundary surface towards the end portion in the substrate,

the taper portion of the first region has a taper ratio greater than a taper ratio of the taper portion of the second region, and

in the step of aligning the optical semiconductor device and the optical waveguide device, the first optical waveguide of the optical semiconductor device is optically coupled with the second optical waveguide of the optical waveguide device.

2. The method according to claim 1, wherein

the guide pin includes an end portion that has an end surface and a taper portion having a diameter that decreases towards the end surface,

the taper ratio of the taper portion of the first region is greater than a taper ratio of the taper portion of the end portion of the guide pin, and

the taper ratio of the taper portion of the end portion of the guide pin is greater than the taper ratio of the taper portion of the second region.

3. The method according to claim 2,

wherein, in the step of aligning the optical semiconductor device and the optical waveguide device by inserting the guide pin into the through-hole and the recess, the guide pin is in contact with the through-hole, and the end portion of the guide pin is in contact with the recess at the boundary surface.

4. The method for producing an optical assembly, comprising the steps of:

forming an optical semiconductor device having a first principal surface and a first back surface opposite to the first principal surface, the optical semiconductor device including a substrate, a recess formed in the first principal surface, and first optical waveguide formed on the substrate, the recess having a first center axis substantially orthogonal to the first principal surface;

forming an optical waveguide device having a second principal surface and a second back surface opposite to the second principal surface, the optical waveguide device including a through-hole having a second center axis substantially orthogonal to the second back surface, and a second optical waveguide, the through-hole penetrating through the second principal surface and the second back surface;

positioning the optical semiconductor device and the optical waveguide device so that the first principal surface and the second back surface face each other; aligning the optical semiconductor device and the optical waveguide device by inserting a guide pin into the through-hole and the recess, the first center axis of the recess and the second center axis of the through-hole being aligned with each other; and

joining the optical semiconductor device and the optical waveguide device to each other, wherein

the recess extends from the first principal surface to a middle portion of the substrate,

in the step of aligning the optical semiconductor device and the optical waveguide device, the first optical

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waveguide of the optical semiconductor device is optically coupled with the second optical waveguide of the optical waveguide device,

the optical semiconductor device further includes an electric wiring structure formed on the substrate,

the electric wiring structure includes an electric wiring section and a moisture-proof structure,

the moisture-proof structure is formed between the electric wiring section and the recess so as to surround the recess, and

the moisture-proof structure is embedded in an insulating film.

5. The method according to claim 4,

wherein the moisture-proof structure includes a metallic layer that is the same as that of the electric wiring section.

6. The method according to claim 1,

wherein the optical semiconductor device includes a plurality of the recesses,

the optical waveguide device includes a plurality of the through-holes, and

the optical semiconductor device and the optical waveguide device are aligned by inserting one of the guide pins into each of the through-holes and each of the recesses.

7. The method according to claim 1, wherein the optical semiconductor device and the optical waveguide device are joined to each other using resin or solder while the guide pin is inserted in the through-hole and the recess.

8. A method for producing an optical assembly, comprising the steps of:

forming an optical semiconductor device having a first principal surface and a first back surface opposite to the first principal surface, the optical semiconductor device including a substrate, a recess formed in the first principal surface, and a first optical waveguide formed on the substrate, the recess having a first center axis substantially orthogonal to the first principal surface;

forming an optical waveguide device having a second principal surface and a second back surface opposite to the second principal surface, the optical waveguide device including a through-hole having a second center axis substantially orthogonal to the second back surface, and a second optical waveguide, the through-hole penetrating through the second principal surface and the second back surface;

inserting a guide pin into the recess of the optical semiconductor device;

positioning the optical semiconductor device and the optical waveguide device so that the first principal surface and the second back surface face each other by sliding the optical waveguide device while the guide pin is fitted into the through-hole of the optical waveguide device, the first center axis of the recess and the second center axis of the through-hole being aligned with each other; and

joining the optical semiconductor device and the optical waveguide device to each other, wherein

the recess extends from the first principal surface to an end portion in a middle portion of the substrate,

the recess includes a first region and a second region arranged adjacent to the first region,

the first region has an opening at the first principal surface and a taper portion having a diameter that increases from a boundary surface between the first region and the second region towards the first principal surface, the boundary surface being in the substrate,

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the second region has the end portion of the recess in the substrate and a taper portion having a diameter that decreases from the boundary surface towards the end portion in the substrate,

the taper portion of the first region has a taper ratio greater than a taper ratio of the taper portion of the second region, and

in the step of positioning the optical semiconductor device and the optical waveguide device, the first optical waveguide of the optical semiconductor device is optically coupled with the second optical waveguide of the optical waveguide device.

9. The method according to claim 8, wherein

the guide pin includes an end portion having an end surface and a taper portion having a diameter that decreases towards the end surface,

the taper ratio of the taper portion of the first region is greater than a taper ratio of the taper portion of the end portion of the guide pin, and

the taper ratio of the taper portion of the end portion of the guide pin is greater than the taper ratio of the taper portion of the second region.

10. A method for producing an optical assembly, comprising the steps of:

forming an optical semiconductor device having a first principal surface and a first back surface opposite to the first principal surface, the optical semiconductor device including a substrate, a recess formed in the first principal surface, and a first optical waveguide formed on the substrate, the recess having a first center axis substantially orthogonal to the first principal surface;

forming an optical waveguide device having a second principal surface and a second back surface opposite to the second principal surface, the optical waveguide device including a through-hole having a second center axis substantially orthogonal to the second back surface, and a second optical waveguide, the through-hole penetrating through the second principal surface and the second back surface;

inserting a guide pin into the recess of the optical semiconductor device;

positioning the optical semiconductor device and optical waveguide device so that the first principal surface and the second back surface face each other by sliding the optical waveguide device while the guide pin is fitted into the through-hole of the optical waveguide device, the first center axis of the recess and the second center axis of the through-hole being aligned with each other; and

joining the optical semiconductor device and the optical waveguide device to each other, wherein

the recess extends from the first principal surface to the middle portion of the substrate,

in the step of positioning the optical semiconductor device and the optical waveguide device, the first optical waveguide of the optical semiconductor device is optically coupled with the second optical waveguide of the optical waveguide device,

the optical semiconductor device further includes an electric wiring structure formed on the substrate,

the electric wiring structure includes an electric wiring section and a moisture-proof structure,

the moisture-proof structure is formed between the electric wiring section and the recess so as to surround the recess and

the moisture-proof structure is embedded in an insulating film.

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11. The method according to claim 4, wherein the optical semiconductor device includes a plurality of the recesses,

the optical waveguide device includes a plurality of the through-holes, and

the optical semiconductor device and the optical waveguide device are aligned by inserting one of the guide pins into each of the through-holes and each of the recesses.

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12. The method according to claim 4, wherein the optical semiconductor device and the optical waveguide device are joined to each other using resin or solder while the guide pin is inserted in the through-hole and the recess.

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